Microprocessor SPARClite смоз

32-bit Embedded Controller MB86830 Series

MB86831/832/833/834/835/836

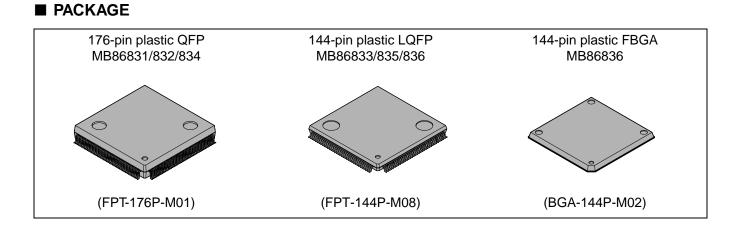
DESCRIPTION

The MB86830 series is a SPARClite ^{*1} series of RISC architecture processors, providing high performance for a variety of embedded applications. Conforming to the SPARC ^{*2} architecture, the MB86830 series is upward codecompatible with the conventional products in the SPARClite family. When running at 100 MHz, the MB86830 series provides performance of 121 VAX-MIPS.

The MB86830 series has on-chip data and instruction caches, allowing the processor to operate independently of the wait time for external memory. The independent instruction bus and internal data bus serve as high-bandwidth interfaces between the IU (integer unit) and caches. The MB86830 series also contains an internal multiplier circuit that facilitates interfacing with external devices, thereby providing high performance with continuous cache hits. The DRAM controller supports both of EDO and fast-page mode DRAMs. The interrupt controller (IRC) supports eight channels of interrupts, allowing a trigger mode and mask to be set for each of the channels. To get the most out of the system with a minimum number of external circuits, the MB86830 series supports chip select output, programmable wait state generator, and page mode DRAM interfaces.

The combination of these features of the MB86830 series achieves high levels of speed, flexibility, and efficiency, making it a line of ideal controllers for a variety of low-cost, high-performance embedded systems.

- *1: SPARClite is a trademark of SPARC International, Inc. in the United States. Fujitsu Microelectronics, Inc. has been granted permission to use the trademark.
- *2 : SPARC is a registered trademark of SPARC International, Inc. in the United States. SPARC is based on technology developed by Sun Microsystems, Inc.



■ FEATURES

- IU (integer unit) Maximum operating frequency : 120 MHz SPARC architecture V8E conforming With 32-bits general register :136 / register window : 8
- Instruction cash
 The entry lock function is supported
 Data cache
 - No cash controlling function supported The entry lock function is supported
- BIU (bus interface unit)
 Purifetchi baffa :1
 Write buffer :4
 The burst mode is supported
 Programmable chip selection function :6
 Programmable weight state control :6
 For 8/16/32-bits bus
 Automatic insertion function of idling cycle after ROM region is accessed
 For burst mode ROM
- With internal clock multiplication circuit
- Sleep mode (low power consumption mode) supported
- With DRAM controller (except on the MB86836)
- With interrupt request controller (IRC)
- On-chip general-purpose 16-bit timer (MB86836 only):1 channel (equivalent to the MB86942)
- Support for the JTAG test port (MB86836 only)

■ PRODUCT LINEUP

Part number	MB86831	MB86832	MB86833	MB86834	MB86835	MB86836	
CPU maximum frequency (MHz)	66/80	66/80/100	66	108/120	84	90/108*1	
BUS maximum frequency (MHz)	2	10	33		40		
Ancillary Version Register	(0000)16	(0001)16	(0002)16	(0003)16	(0004)16	(0001)16	
Instruction cache	4 KB/2 way	8 KB/2 way	1 KB/Direct	16 KB/2 way	4 KB/2 way	8 KB/2 way	
Data cache	2 KB/2 way	8 KB/2 way	1 KB/Direct	16 KB/2 way	2 KB/2 way	8 KB/2 way	
Cache size change function	No	8/4/2/1 KB selectable		No			
ADR pin	ADR	<27:2>	ADR<23:2>	ADR<27:2>	ADR<	23:2>	
ADR enhancement (ASISEL)	No	ADR<31:2>	ADR<27:2>	ADR<31:2>	ADR<	27:2>	
Clock gear function	No						
DSU	No	Yes	No	Yes	N	No	
DRAM controller	4bank		1bank	4bank	1bank	No	
JTAG test port			No			Yes	
General porpose 16-bit timer*2			No	1ch			
Internal pull-up/down resister pin	P63	P63, P162 to P164			P41 to P44, P79		
Internal power supply (VDD3)		3.3 V		2.5 V	3.3 V	2.5 V	
I/O power supply (VDD5)		3.3 V to 5.0 V	/		3.3 V		
Package	FPT-17	⁻ P176 76P-M01 24 mm	LQFP144 FPT-144P- M08	SQFP176 FPT-176P- M01	LQFP144 FPT-144P- M08	LQFP144 FPT-144P- M08 20 × 20 mm FBGA144	
	27 / 1		20 × 20 mm	24 × 24 mm	20×20 mm	BGA- 144P-M02 12 × 12 mm	

*1:MB86836 108 MHz version is under developement.

*2: The general-purpose timer on the MB86836 is a subset of the prescaler-integrated 16-bit timer on the MB86942. For the type supporting only the internal clock mode, refer to the document for the MB86941/942.

■ FOR PACKAGE AND PART NUMBER

Package	MB86831	MB86832	MB86833	MB86834	MB86835	MB86836
FPT-176P-M01	Yes	Yes	No	Yes	No	No
FPT-144P-M08	No	No	Yes	No	Yes	Yes
BGA-144P-M02	No	No	No	No	No	Yes

Note:Refer to "PACKAGE DIMENSIONS" for details in each package.

■ DIFFERENCES

1.Package

- MB86831/832/834 : QFP176
- MB86833/835/836 : LQFP144
- MB86836 : FBGA144

2.Pin array

- MB86831/832/834: The pin is interchangeable. However, the terminal of MB86834 is the pull-up resistor none.
- MB86833/835 : The pin is interchangeable.
- MB86836 : MB86833/835, from which DRAMC related pins are deleted and to which one channel of general-purpose 16-bit timer and the JTAG pin are added.

3.Maximum operation frequency

- MB86831 : 66MHz/80MHz
- MB86832 : 66MHz/80MHz/100MHz
- MB86833 : 66MHz
- MB86834 : 108MHz/120MHz
- MB86835 : 84MHz
- MB86836 : 90MHz/108MHz

4. Power-supply voltage

Power-supply voltage	MB86831	MB86832	MB86833	MB86834	MB86835	MB86836
Internal power-supply voltage		3.3 V		2.5 V	3.3 V	2.5 V
I/O power-supply voltage		3.3 V or 5.0 V		3.3 V	3.3 V	3.3 V

* : The power-supply voltage is different (Refer to "ELECTRIC CHARACTERISTICS") depending on the condition of the operation frequency.

5.Cache memory

Cache memory	MB86831	MB86832	MB86833	MB86834	MB86835	MB86836
Instruction cash	4 KB/2 way	8 KB/2 way	1 KB/Direct	16 KB/2 way	4 KB/2 way	8 KB/2 way
Data cash	2 KB/2 way	8 KB/2 way	1 KB/Direct	16 KB/2 way	2 KB/2 way	8 KB/2 way

6.Register

Register name	MB86831/832/833/835/836	MB86834
Instruction Cache Invalidate Register (ICINVLD)	Map of ASI = 0x0c, ADR = 0x00001000(Bank1) ASI = 0x0c, ADR = 0x80001000(Bank2)	Map of ASI = 0x0c, ADR = 0x00008000(Bank1) ASI = 0x0c, ADR = 0x80008000(Bank2)
Data Cache Invalidate Register (DCINVLD)		Map of ASI = 0x0e, ADR = 0x00008000(Bank1) ASI = 0x0e, ADR = 0x80008000(Bank2)

Register name	MB86831	MB86832	MB86833	MB86834	MB86835	MB86836
Ancillary Version Register (VER2)	(00) 16	(01)16	(02)16	(03)16	(04)16	(01)16

7.Clock gear

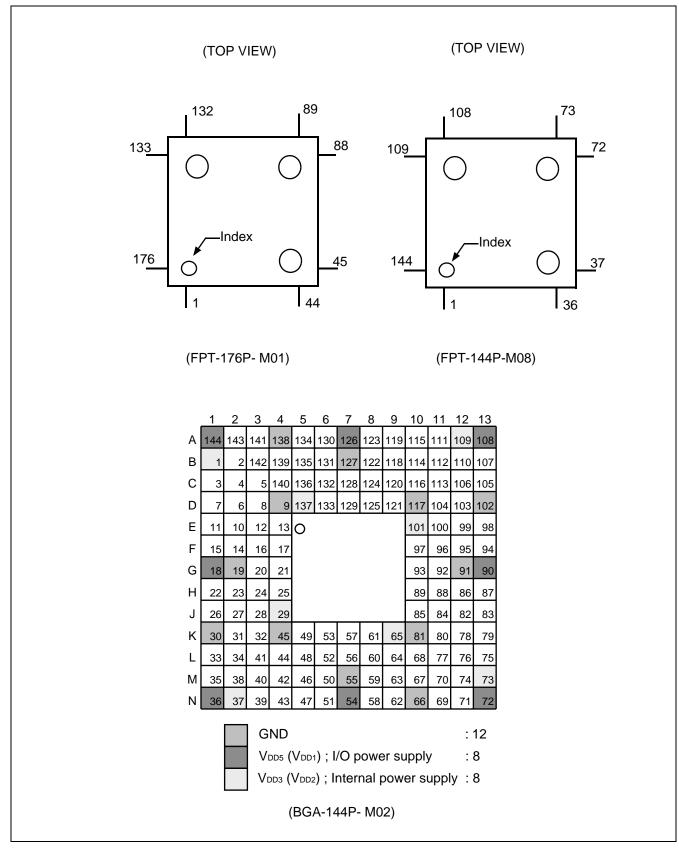
- MB86832/833/834/835/836 : Supported
- MB86831 : No supported

8.External signal

Item	MB86831	MB86832	MB86833	MB86834	MB86835	MB86836	
ASISEL pin function	No	Multiplex of ADR<31:28> and ASI<3:0>	Multiplex of ADR<27:24> and ASI<3:0>	Multiplex of ADR<31:28> and ASI<3:0>	•	R<27:24> and :3:0>	
DSU (debugging support unit)	No	Yes	No	Yes	Ν	lo	
DRAM controller	4Bank supported	4Bank supported	1Bank supported*	4Bank supported	1Bank supported*	No	
General-purpose 16-bit timer			No			Wih 1ch. prescaler (Equivalent to MB86942)	
JTAG			No			Support	
Pull-up resistor or pull-down resistor	Inclusion	Inclusion No					

*:RAS1# to RAS3# and DWE1# to DWE3# deletion.

■ PIN ASSIGNMENT



• MB86831/832/834

Pin no.	Pin symbol	Pin no.	Pin symbol	Pin no.	Pin symbol	Pin no.	Pin symbol	Pin no.	Pin symbol
1	V _{DD3}	37	D<4>	73	BMREQ#	109	ADR<11>	145	FLOAT#
2	D<31>	38	BMODE8#	74	OVF#	110	READY#	146	PDOWN#
3	D<30>	39	Vss	75	SAMEPAGE#	111	Vdd3	147	WKUP#
4	D<29>	40	D<3>	76	AS#	112	ADR<12>	148	RESET#
5	D<28>	41	D<2>	77	Vdd3	113	ADR<13>	149	Vss
6	Vss	42	D<1>	78	RDWR#	114	ADR<14>	150	IDLEEN
7	BMODE16#	43	D<0>	79	RDYOUT#	115	ADR<15>	151	CLKSEL1
8	D<27>	44	V _{DD3}	80	CS5#	116	Vss	152	CLKSEL0
9	D<26>	45	Vss	81	CS4#	117	ADR<16>	153	CLKEXT
10	D<25>	46	DWE3#	82	Vdd5	118	ADR<17>	154	CLKIN
11	D<24>	47	DWE2#	83	Vss	119	ADR<18>	155	Vdd5
12	Vdd5	48	DWE1#	84	CS3#	120	ADR<19>	156	IRQ11
13	D<23>	49	DWE0#	85	CS2#	121	Vdd5	157	IRQ10
14	D<22>	50	Vss	86	CS1#	122	ADR<20>	158	IRQ9
15	D<21>	51	V _{DD5}	87	CS0#	123	ADR<21>	159	IRQ8
16	D<20>	52	RAS0#	88	Vss	124	ADR<22>	160	Vss
17	Vss	53	RAS1#	89	Vdd3	125	ADR<23>	161	Reserved
18	D<19>	54	RAS2#	90	BE3#	126	MEXC#	162	[ASISEL *]
19	D<18>	55	RAS3#	91	BE2#	127	Vss	163	[EMUBRK# *]
20	D<17>	56	V _{DD3}	92	BE1#	128	ADR<24>	164	[EMUENB# *]
21	D<16>	57	CAS0#	93	BE0#	129	ADR<25>	165	V _{DD3}
22	BTEST#	58	CAS1#	94	Vss	130	ADR<26>	166	[EMUSD3]
23	V _{DD3}	59	CAS2#	95	NONCACHE#	131	ADR<27>	167	[EMUSD2]
24	D<15>	60	CAS3#	96	Reserved	132	Vdd3	16	[EMUSD1]
25	D<14>	61	Vss	97	Reserved	133	Vss	169	[EMUSD0]
26	D<13>	62	DOE#	98	ADR<2>	134	ASI<3>[/ADR<28>]	170	Vdd5
27	D<12>	63	CLKSEL2 *	99	ADR<3>	135	ASI<2>[/ADR<29>]	171	Vss
28	Vss	64	ERROR#	100	Vdd5	136	ASI<1>[/ADR<30>]	172	[EMUD3]
29	D<11>	65	LOCK#	101	ADR<4>	137	ASI<0>[/ADR<31>]	173	[EMUD2]
30	D<10>	66	CTEST#	102	ADR<5>	138	Vss	174	[EMUD1]
31	D<9>	67	V _{DD5}	103	ADR<6>	139	Vdd5	175	[EMUD0]
32	D<8>	68	BREQ#	104	ADR<7>	140	IRL<3>/IRQ15	176	Vss
33	V _{DD5}	69	PBREQ#	105	Vss	141	IRL<2>/IRQ14		·
34	D<7>	70	BGRNT#	106	ADR<8>	142	IRL<1>/IRQ13		
35	D<6>	71	BMACK#	107	ADR<9>	143	IRL<0>/IRQ12	ŀ	
36	D<5>	72	Vss	108	ADR<10>	144	V _{DD3}	ŀ	

V_{DD3} :For internal power supply. V_{DD5} :For I/O power supply.

Reserved:This pin must be open. *:The pull-up resistor is built into. However, there is no pull-up resistor in MB86834. []:Pin is added with MB86832/834. Please use this terminal by the opening in case of MB86831-66 and 80.

• MB86833/835

Pin no.	Pin symbol	Pin no.	Pin symbol	Pin no.	Pin symbol	Pin no.	Pin symbol
1	Vdd3	37	Vdd3	73	Vdd3	109	Vdd3
2	BMODE16#	38	D<2>	74	BE3#	110	MEXC#
3	D<28>	39	D<1>	75	BE2#	111	ADR<23>
4	D<27>	40	D<0>	76	BE1#	112	ASI<3>/ADR<24>
5	D<26>	41	DWE0#	77	BE0#	113	ASI<2>/ADR<25>
6	D<25>	42	RAS0#	78	Reserved	114	ASI<1>/ADR<26>
7	D<24>	43	CAS0#	79	Reserved	115	ASI<0>/ADR<27>
8	D<23>	44	CAS1#	80	NONCACHE#	116	IRL<3>/IRQ15
9	Vss	45	Vss	81	Vss	117	Vss
10	D<22>	46	CAS2#	82	ADR<2>	118	IRL<2>/IRQ14
11	D<21>	47	CAS3#	83	ADR<3>	119	IRL<1>/IRQ13
12	D<20>	48	DOE#	84	ADR<4>	120	IRL<0>/IRQ12
13	D<19>	49	ERROR#	85	ADR<5>	121	FLOAT#
14	D<18>	50	LOCK#	86	ADR<6>	122	PDOWN#
15	D<17>	51	CTEST#	87	ADR<7>	123	WKUP#
16	D<16>	52	BREQ#	88	ADR<8>	124	RESET#
17	BTEST#	53	PBREQ#	89	ADR<9>	125	IDLEEN
18	Vdd5	54	Vdd5	90	Vdd5	126	Vdd5
19	Vss	55	Vss	91	Vss	127	Vss
20	D<15>	56	BGRNT#	92	ADR<10>	128	CLKSEL2
21	D<14>	57	BMACK#	93	ADR<11>	129	CLKSEL1
22	D<13>	58	BMREQ#	94	ADR<12>	130	CLKSEL0
23	D<12>	59	OVF#	95	ADR<13>	131	CLKEXT
24	D<11>	60	SAMEPAGE#	96	ADR<14>	132	CLKIN
25	D<10>	61	AS#	97	ADR<15>	133	IRQ11
26	D<9>	62	RDWR#	98	ADR<16>	134	IRQ10
27	D<8>	63	RDYOUT#	99	ADR<17>	135	IRQ9
28	BMODE8#	64	CS5#	100	READY#	136	IRQ8
29	Vdd3	65	V _{DD3}	101	Vdd3	137	Vdd3
30	Vss	66	Vss	102	Vss	138	Vss
31	D<7>	67	CS4#	103	ADR<18>	139	Reserved
32	D<6>	68	CS3#	104	ADR<19>	140	ASISEL
33	D<5>	69	CS2#	105	ADR<20>	141	D<31>
34	D<4>	70	CS1#	106	ADR<21>	142	D<30>
35	D<3>	71	CS0#	107	ADR<22>	143	D<29>
36	Vdd5	72	V _{DD5}	108	Vdd5	144	Vdd5

V_{DD3} :For internal power supply. V_{DD5} :For I/O power supply. Reserved:This pin must be open.

• MB86836

Pin no.	Pin symbol	Pin no.	Pin symbol	Pin no.	Pin symbol	Pin no.	Pin symbol
1	Vdd3	37	Vdd3	73	Vdd3	109	V _{DD3}
2	BMODE16#	38	D<2>	74	BE3#	110	MEXC#
3	D<28>	39	D<1>	75	BE2#	111	ADR<23>
4	D<27>	40	D<0>	76	BE1#	112	ASI<3>/ADR<24>
5	D<26>	41	TRST#	77	BE0#	113	ASI<2>/ADR<25>
6	D<25>	42	TCK*	78	VPD	114	ASI<1>/ADR<26>
7	D<24>	43	TMS*	79	IN0	115	ASI<0>/ADR<27>
8	D<23>	44	TDI*	80	NONCACHE#	116	IRL<3>/IRQ15
9	Vss	45	Vss	81	Vss	117	Vss
10	D<22>	46	TDO	82	ADR<2>	118	IRL<2>/IRQ14
11	D<21>	47	OUT0	83	ADR<3>	119	IRL<1>/IRQ13
12	D<20>	48	PRSCK0	84	ADR<4>	120	IRL<0>/IRQ12
13	D<19>	49	ERROR#	85	ADR<5>	121	FLOAT#
14	D<18>	50	LOCK#	86	ADR<6>	122	PDOWN#
15	D<17>	51	CTEST#	87	ADR<7>	123	WKUP#
16	D<16>	52	BREQ#	88	ADR<8>	124	RESET#
17	BTEST#	53	PBREQ#	89	ADR<9>	125	IDLEEN
18	Vdd5	54	Vdd5	90	Vdd5	126	Vdd5
19	Vss	55	Vss	91	Vss	127	Vss
20	D<15>	56	BGRNT#	92	ADR<10>	128	CLKSEL2
21	D<14>	57	BMACK#	93	ADR<11>	129	CLKSEL1
22	D<13>	58	BMREQ#	94	ADR<12>	130	CLKSEL0
23	D<12>	59	OVF#	95	ADR<13>	131	CLKEXT
24	D<11>	60	SAMEPAGE#	96	ADR<14>	132	CLKIN
25	D<10>	61	AS#	97	ADR<15>	133	IRQ11
26	D<9>	62	RDWR#	98	ADR<16>	134	IRQ10
27	D<8>	63	RDYOUT#	99	ADR<17>	135	IRQ9
28	BMODE8#	64	CS5#	100	READY#	136	IRQ8
29	Vdd3	65	Vdd3	101	Vdd3	137	V _{DD3}
30	Vss	66	Vss	102	Vss	138	Vss
31	D<7>	67	CS4#	103	ADR<18>	139	Reserved
32	D<6>	68	CS3#	104	ADR<19>	140	ASISEL
33	D<5>	69	CS2#	105	ADR<20>	141	D<31>
34	D<4>	70	CS1#	106	ADR<21>	142	D<30>
35	D<3>	71	CS0#	107	ADR<22>	143	D<29>
36	Vdd5	72	Vdd5	108	Vdd5	144	V _{DD5}
רחס/	0.5.1/		lving internal po		VPD Test pin U	a alle . C a	

VDD3 : 2.5-V power pin (for supplying internal power)

VPD: Test pin. Usually fixed to the L level. * : With an internal pull-down resistor

VDD5 : 3.3-V power pin (for supplying I/O power)

Reserved : Leave the pin open.

9

■ PIN DESCRIPTION

1. CPU Core Related Pins

Symbol	Pin name	I/O			F	unctior	า		
CLKIN	CLOCK	I		gulat	es external bus ased on the clo		ion.The	bus AC characte	ristics
CLKEXT	EXTERNAL CLOCK BYPASS	Ι	PLL circuit; th	at thi neC"l	s pin selects th	the exte	ernal clo	enerated by the in ock signal (input th e "L" level.	
RESET#	SYSTEM RESET	I	Reset input. The "L" inpu	t to t	his pin initialize	es the C	PU.		
				re us	sed to set the II			and cache operat external clock frequ	
			CLKSEI	L2	CLKSEL1	CLK	SEL0	Internal clock	
CLKSEL0			Н		L		L	×1	
CLKSEL1	INTERNAL CLOCK SELECT	Ι	Н		L		Н	×2	
CLKSEL2			Н		Н		L	×3	
			Н		Н		Н	×4	
			L		Н		Н	×5	
			Any other se	ttina	is prohibited.	1			
ASISEL	ADDRESS SPACE IDENTI-	I	Setting this p grant state.	cts th	, this pin is pull	he "L" i ed up w	vith a re	the AS# pin in the	
	FIERS SELECT		ASISEL	ASI	MB86832/834 <3:0>/ADR<28		MB86833/835/836 > ASI<3:0>/ADR<24:27>		
			L		ADR<28:31>			ADR<24:27>	
			Н		ASI<3:0>			ASI<3:0>	
CTEST# BTEST#	CTEST BTEST	I	Test pins. Fix these pin	s usi	ually to the "H"	level.			
ADR<27:2> or ADR<23:2> (MB86833/ 835/836)	ADDRESS BUS	I/O	Fix these pins usually to the "H" level. Address pin. The ADR<27:2>pin (ADR<23:2>pin on the MB86833/835/836)handles the signal for identifying an instruction address or data address.For us- ing the 8/16-bit bus width, ADR<1> and ADR<0> are output multiplexed with BE2# and BE3#, respectively.This pin remains enabled during the bus cycle; the value output during the idle cycle is not guaranteed. In the bus grant state, the pin serves as an input used, e.g., by the CS generator circuit (while the "L" input to the AS# pin is prohibited with the ASISEL pin at the "L" level) and ADR<31:28> (ADR<31:24> on the MB86833/835/836) is handled internally as 0.						

(Continued)

AS# ADDRESS STROBE I/O Address strobe signal. This pin outputs the "L" level signal for the first bus cycle. Basically, the bus cycle starts with the AS# signal asserted and ends up with the BUS RDWR# READ/WRITE BUS TRANSACTION I/O Read/write signal. This pin outputs the "L" level signal when the current bus cycle is the write cycle or the "L" level signal when the current bus cycle is the ginning to end. In the bus grant state, the pin serves as an input used for the signals to actuate the CS generator and wait state generator circuits. READ/WRITE BUS TRANSACTION I/O Read/write signal. This pin outputs the "L" level signal when the current bus cycle is the write cycle or the "H" level signal when the current bus cycle is the ginning to end. In the bus grant state, the pin serves as an input used for generating the DWE0#-DWE3# and DOE# signals to enable the DRAM controller. The signal at this pin is not used when the DRAM controller is disabled Bye enable signals. These pins are used to indicate the bytes valid for in write mode when the 32-bit bus width is used. In the bus grant state, the pins erneain enabled the DRAM controller. The signal at this pin is not used Mhen the DRAM controller is disabled In read mode, all of the BE0# to BE3# signals are asserted regardless of the data type. For the 8-bit or 16-bit bus width, the BE2# and BE3# pins output ADR<1> and ADR<0>, respectively. The BE0# to BE3# pins remain enabled during the bus cycle; the out- put level during the idle cycle is not guaranted. In the bus grant state, the pins enter the High-Z state and, only when the DRAM controller is on with the 16-bit bus width used, the BE2# pins serves as the ADR<1> input pin. BE0# BE1# BE2# BYTE ENABLE Im the bus grant state, the pins en	Symbol	Pin name	I/O			Function					
AS# ADDRESS STROBE I/O This pin outputs the "L" level signal for the first bus cycle. Basically, the Bus cycle starts with the AS# signal asserted and ends up with the READYW or RDYCUT# signal asserted. In the bus grant state, the pin serves as an input used for the signals to actuate the CS generator and wait state generator circuits. READ/WRITE BUS TRANSACTION I/O Read/write signal. This pin outputs the "L" level signal when the current bus cycle is the write cycle or the "H" level signal when it is the read or idle cycle. The output level remains at "H" or"L" during the entire bus cycle from the be ginning to end. In the bus grant state, the pin serves as an input used for generating the DWEd#-DWE3# and DCE# signals to enable the DRAM controller. The signal at this pin is not used when the DRAM controller is disabled lin read mode, all of the BE0# to BE3# signals are asserted regardless of the data type. For the 8-bit or 16-bit bus width, the BE2# and BE3# pins output ADR<1> and ADRCA>, respectively. The BE0# to BE3# pins remain enabled during the bus cycle; the out put level during the idle cycle is not guaranted. In the bus grant state, the pins enter the High-Z state and, only when the DRAM controller is on with the 16-bit bus width used, the BE2# pins serves as the ADR<1> input pin. BE0# BE1# BE1# BE1# BE3# BYtE ENABLE VO O Vidth of 32-bits bus Byte-0 (O<31:24>)* 0 1 1 1 0 1 Byte-2 (D<15:8>) 1 1 0 1 1 Half word-0(D<31:16>) 0 0 1 1 Half word-0(D<31:16>) 1 0 1 1 Half word-0(D<31:16>) 0 0 0 0 0	D<31:0>	DATA BUS	I/O	This pin products of the aligned half words multiples of are used in 16-bit bus not which is not set.	ovides a and data at addro and doo f the nu the 8-b mode, a	a store operations. Instruct esses which are multiples uble words must be aligne mbers 2 and 8, respective it and 16-bit bus modes, re pull-up resistor must be c	ctions of the ed at a ely. D- espect connect	and w numl ddres <7:0> ively. cted to	ord da ber 4. ses wl and D For us b the d	hich are hich are 0<15:0> se in the lata bus	
RDWR#READ/WRITE BUS TRANSACTIONI/OThis pin outputs the "L" level signal when the current bus cycle is the write cycle or the "H" level signal when it is the read or idle cycle. The output level remains at "H" or"L" during the entire bus cycle from the be ginning to end. In the bus grant state, the pin serves as an input used for generating the DWE0#-DWE3# and DOE# signals to enable the DRAM controller. The signal at this pin is not used when the DRAM controller is disabled Bye enable signals. These pins are used to indicate the bytes valid for in write mode when the 32-bit bus width is used. In the bus grant state, the pins enter the BE3# signals are asserted regardless of the data type. For the 8-bit or 16-bit bus width, the BE2# and BE3# pins output ADR<1> and ADR<0>, respectively. The BE0# to BE3# pins remain enabled during the bus cycle; the out- put level during the idle cycle is not guaranteed. In the bus grant state, the pins enter the High-Z state and, only when the DRAM controller is on with the 16-bit bus width used, the BE2# pins serves as the ADR<1> input pin.BE0# BE1# BE2# BE3#Width of 32-bits busWrite Width of 32-bits busByte-0 (D<31:24>) * 0 1 1 1 1 Byte-1 (D<23:16>) 1 0 1 1 1 Half word-0(D<31:16>) 0 0 1 1 1 Half word-0(D<31:16>) 0 0 1 1 1 Half word-0(D<31:16>) 0 0 1 1 1 Half word-0(D<31:16>) 0 0 1 1 1 1 Half word-0(D 0 <td>AS#</td> <td></td> <td>I/O</td> <td>This pin ou bus cycle s READY# o In the bus g</td> <td>tputs the starts wi r RDYC grant sta</td> <td>e "L" level signal for the firs th the AS# signal asserted UT# signal asserted. ite, the pin serves as an in</td> <td>d and put us</td> <td>ends i ed for</td> <td>up witl the si</td> <td>h the</td>	AS#		I/O	This pin ou bus cycle s READY# o In the bus g	tputs the starts wi r RDYC grant sta	e "L" level signal for the firs th the AS# signal asserted UT# signal asserted. ite, the pin serves as an in	d and put us	ends i ed for	up witl the si	h the	
BEO# BYTE ENABLE O	RDWR#	BUS	I/O	This pin outputs the "L" level signal when the current bus cycle is the write cycle or the "H" level signal when it is the read or idle cycle. The output level remains at "H" or "L" during the entire bus cycle from the beginning to end.							
BE1# BYTE ENABLE O I/O I/O I/O Bus Access type Bet# Bet# <td>BE0#</td> <td></td> <td></td> <td colspan="8">Bye enable signals. These pins are used to indicate the bytes valid for in write mode with 32-bit bus width is used. In read mode, all of the BE0# to BE3# signals are asserted regard of the data type. For the 8-bit or 16-bit bus width, the BE2# and B pins output ADR<1> and ADR<0>, respectively. The BE0# to BE3# pins remain enabled during the bus cycle; the put level during the idle cycle is not guaranteed. In the bus grant state, the pins enter the High-Z state and, only with DRAM controller is on with the 16-bit bus width used, the BE2 serves as the ADR<1> input pin.</td>	BE0#			Bye enable signals. These pins are used to indicate the bytes valid for in write mode with 32-bit bus width is used. In read mode, all of the BE0# to BE3# signals are asserted regard of the data type. For the 8-bit or 16-bit bus width, the BE2# and B pins output ADR<1> and ADR<0>, respectively. The BE0# to BE3# pins remain enabled during the bus cycle; the put level during the idle cycle is not guaranteed. In the bus grant state, the pins enter the High-Z state and, only with DRAM controller is on with the 16-bit bus width used, the BE2 serves as the ADR<1> input pin.							
BE3# O Vidth of 32-bits bus Write Byte-0 (D<31:16>) 1 0 1 1 Half word-0(D<31:16>) 0 0 1 1 0 1 Half word-1(D<15:0>) 1 1 0 0 1 1 Half word-1(D<15:0>) 1 1 0 0 0 Half word-1(D<15:0>) 1 1 0 0 Write Read All data types 0 0 0	BE1# BE2#	BYTE ENABLE		bus							
Width of 32-bits bus Write Byte-2 (D<15:8>) 1 1 0 1 Half word-0(D<31:16>) 0 0 1 1 1 0 Write Byte-3 (D<7:0>) 1 1 1 0 1 Half word-0(D<31:16>) 0 0 1 1 1 1 Half word-1(D<15:0>) 1 1 0 0 0 0 Word 0 0 0 0 0 0 0 Read All data types 0 0 0 0 0	BE3#					· · ·				-	
Width of 32-bits bus Write Byte-3 (D<7:0>) 1 1 1 0 Half word-0(D<31:16>) 0 0 1						, , , , , , , , , , , , , , , , , , ,					
32-bits 32-bits Half word-0(D<31:16>) 0 0 1 1 Half word-1(D<15:0>) 1 1 0 0 Word 0 0 0 0 Read All data types 0 0 0				Width of	\N/rito	· · ·				-	
Half word-1(D<15:0>) 1 1 0 0 Word 0 0 0 0 0 Read All data types 0 0 0 0				32-bits	VVIILE						
Word 0 0 0 0 Read All data types 0 0 0 0						,					
ReadAll data types000						, , , , , , , , , , , , , , , , , , ,				-	
					Read			-	_		

(Continued)

Symbol	Pin name	I/O	Function						
			Width of	(Continued) Width of Access type BE0# BE1# BE2#					BE3#
					Byte-0 (D<15:8>)	1	0	0	0
					Byte-1 (D<7:0>)	0	1	0	0
					Byte-2 (D<15:8>)	1	0	1	0
					Byte-3 (D<7:0>)	0	1	1	0
			Width of	Write	Half word-0 (D<15:0>)	0	0	0	0
			16-bits bus		Half word-1 (D<15:0>)	0	0	1	0
			545		Word (D<15:0>) access-0	0	0	1	0
					Word (D<15:0>)access-1	0	0	0	0
				_	Access-0	0	0	0	0
				Read	Access-1	0	0	1	0
					Byte-0	Х	Х	0	0
BE0#		0			Byte-1	Х	Х	0	1
BE1#	BYTE ENABLE	0			Byte-2	X	Х	1	0
BE2# BE3#		I/O O			Byte-3	Х	Х	1	1
					Half word-0 access-1		Х	0	1
					Half word-0 access-0		Х	0	0
			Width of 8-bits busHalf word-1 access-1XXWord access-0X	vvrite	Half word-1 access-0	Х	Х	1	1
					Half word-1 access-1	Х	Х	1	0
					word access-0	Х	Х	1	1
				Х	Х	1	0		
					word access-2	Х	Х	0	1
					word access-3	Х	Х	0	0
					Access-0	Х	Х	0	0
				Deed	Access-1	Х	Х	0	1
				Read	Access-2	Х	Х	1	0
					Access-3	Х	Х	1	1
	* : The mark such as (D<31:24					oit of t	he dat	a bus	used.
CS0# CS1# CS2# CS3# CS4# CS5#	CHIP SELECT	0	Chip select signals. These chip select signals are asserted when the Address Range Spec- ifier Register (ARSR) and Address Mask Register (AMR) is accessed with the CS Enable bit (bit 4) in the System Support Control Register (SSCR) set to "1." (Note, however, that only the CS0# pin is indepen- dent of the CS Enable bit.)						

(Continued)

Symbol	Pin name	I/O	Function
BREQ#	BUS REQUEST	1	 Bus request signal. When the BREQ# signal is asserted by external bus mastering, the CPU releases the bus as shown below upon termination of the current bus cycle: (1)When executing the Atomic Load Store instruction, the CPU releases es the bus after completing both of loading and storing. (2)When loading or storing a double word: If the BREQ# signal is asserted at the first word, the CPU releases the bus after transfer of the first word. If the bus cycle for the second word, the CPU releases the bus after transfer of the second word, the CPU releases the bus after transfer of the second word. (3)When storing data at the 8/16-bit bus width: The CPU releases the bus after transfer of that size of data which is handled by the instruction (for example, after writing 8-bit data four times when storing word data using an 8-bit bus). (4)When loading data at the 8/16-bit bus width: The CPU releases the bus after transfer of one word. When the ASISEL pin is at the "L" level, the "L" input to the AS# pin is prohibited in the bus grant state.
BGRNT#	BUS GRANT	0	Bus grant signal. Upon reception of a bus request (BREQ#), the BGRNT# signal is as- serted to notify the external device of the bus released status.
IRL3 IRL2 IRL1 IRL0	INTERRUPT RE- QUEST LEVEL	I	Interrupt input pins. These pins are used to input an encoded interrupt level. They handle a group of asynchronous input signals, notifying the IU (integer unit) of an interrupt level only when the same level is detected twice at the fall of an external clock pulse. IRL = 0000 $_2$ and IRL = 1111($_2$) indicate no interrupt and a nonmaskable interrupt as defined in the SPARC archi- tecture. IRL must be determined for priority by an external circuit and must be held until confirmed by the CPU.
READY#	EXTERNAL READY	1	Ready signal input pin. Input the "L" level signal to upon completion of a bus cycle. Upon reception of READY#="L", the CPU starts the next bus cycle. Note, however, that the"L" input to this pin is not necessary when the internal wait state generator circuit is used. For burst transfer, instruction fetch or data load using an 8-bit bus, in- struction fetch or data load using an 16-bit bus, the pin must input the ready signal for the prescribed number of times whenever the address strobe signal is asserted.
MEXC#	MEMORY EXCEPTION	1	Memory access exception pin. If this pin inputs the "L" level signal in the same cycle as the ready sig- nal input, the CPU handles it as an instruction access or data access exception to generate a trap. The operation of the device is unpredict- able if the MEXC# signal is asserted at a timing other than the same cycle as the ready signal input. (An exception occurring with the PSR ET bit set to "0" results in an error state.)

Symbol	Pin name	I/O	Function
ERROR#	ERROR SIGNAL	0	Error signal. This pin outputs an error signal indicating that the CPU has stopped in the error state resulting from a trap occurring with traps disabled. The CPU can exit the error state only by a reset.
ASI<3:0>	ADDRESS SPACE IDENTIFIERS	I/O	ASI pin (address space identification signal) or ADR pin. Setting the ASISEL pin to "H" selects the ASI pin; setting it to "L" selects the ADR<28:31> pin on the MB86832/834 or ADR<24:27> pin on the MB86833/835/836. When the ASISEL pin is set to "L", the "L" input to the AS# pin is prohibited. A choice of these pins is supported by the MB8682/833/834/835/836 but not by the MB86831-66/80 (only ASI<3:0> is available). Like the ADR<27:2> pin (ADR<23:2> pin on the MB86833/835/836), this pin remains enabled for output during the bus cycle. The ASI pin serves as an input in the bus grant state, used for CS generation and internal resource address decoding. When ASI<3:0> is input from an external device, ASI<7:4> is handled as "0" in the CPU.
LOCK#	BUS LOCK	0	Bus lock signal. During execution of the Atomic Load Store instruction, the CPU asserts the LOCK# signal to indicate that the current bus transaction requires multiple transfers which cannot be divided. At a bus request (BREQ#) during execution of an atomic instruction, the CPU releases the bus (by asserting the BGRNT# signal) upon completion of the instruction exe- cution. For normal use (where bus access permission is controlled by BREQ#/BGRNT#), the LOCK# signal need not be used.
RDYOUT#	READY OUTPUT	0	Ready signal output. This pin outputs the composite signal consisting of the ready signal generated by the internal wait state generator circuit and the external ready signal (READY#). While the delay of the internally generated ready signal is regulated based on the clock input, the input from the pin is output delayed as it is at the timing of generation of the external ready signal.
IDLEEN	IDLE ENABLE	I	Idle insertion enable pin. If the cycle that follows access to the CSO# area is load or store oper- ation when this pin is at the "H" level, the CPU starts the next bus cycle after inserting two idle clock cycles. This is efficient when EPROM which takes long data bus output off time is connected directly to the CPU.When this pin is at the "L" level, the CPU inserts only one idle cy- cle before a write cycle immediately after a read cycle (this control is compatible with conventional SPARClite processors). Fix this pin at the "H" or "L" level.
BMODE8# BMODE16#	BOOT MODE 8 BOOT MODE 16	I	CS0# area bus width setting signals. These pins input signals at a reset to determine the bus width of the CS0# area. Setting the BMODE8# pin to "L" selects the 8-bit bus mode; setting the BMODE16# pin to "L" selects the 16-bit bus mode. (The bus width for the CS1#-CS5# area is specified by the Bus Width/ Cacheable Control Register (BWCR).) Fix these pins to "L" or "H". However, it is not allowed to set both of them to "L".

(Continued)

Symbol	Pin name	I/O	Function
NONCACHE#	NON-CACHE- ABLE	I	Non-cacheable signal. This pin inputs the signal for exclusion from data caching. The NON- CACHE# signal is enabled by setting the Cacheability Enable bit (bit 7) in the Cache/BIU Control Register (CBIR). The "L" input to this pin when data is read prevents the data and its address from being written to the data cache (the NONCACHE# signal is disabled at an instruction fetch). Usually, the NONCACHE# signal must be asserted in the cycle in which the address strobe signal is asserted. Even if the NON- CACHE# signal is asserted after a delay of one or more cycles, how- ever, the signal can be used by setting the Non-cacheable bit (bit 9, bit 8) in the Cache/BIU Control Register (CBIR).
PDOWN#	POWER DOWN	0	Sleep mode (low power consumption mode) output pin. "L" level input to this pin releases the CPU from the sleep mode (low power consumption mode) to start operation. Although the pin is an asynchronous input, it requires an "L" width of at least two clock cycles. Input "L" to this pin only when the PDOWN# pin is at the "L" level.
WKUP#	WAKE-UP	I	Sleep mode (low power consumption mode) cancel pin. "L" input to this pin cancels the CPU sleep mode (low power consump- tion mode), causing the CPU to start operation. Although the pin is an asynchronous input, it requires an "L" width of at least two clock cycles. Input the "L" signal to this pin only when PDOWN# is "L". When PDOWN# goes "H", set this pin to "H".
BMREQ#	BURST MODE REQUEST	0	Burst transfer request pin. If a cache miss occurs when the Instruction Burst Enable bit or Data Burst Enable bit in the Bus Control Register (BCR) has been set, the CPU sets the BMREQ# signal to "L" and requests external memory for burst transfer. The BMREQ# signal is also asserted when the DRAM Burst Enable bit in the System Support Control Register (SSCR) has been set. In this case, however, the external device need not return the BMACK# signal because the internal DRAM controller responds to the request.
BMACK#	BURST MODE ACKNOWL- EDGE	I	Burst mode acknowledge input. When a burst transfer request is issued, the burst transfer mode is es- tablished if the "L" level asserted until the same cycle as the READY# signal is input to this pin. (It is also established either when the "L" level is input in the same cycle as the READY# signal or when the "L" level input in an earlier cycle continues until the same cycle as the READY# signal.) When the DRAM Burst Enable bit in the System Support Con- trol Register (SSCR) has been set, the burst transfer mode is estab- lished even though this pin receives the BMACK# signal.
PBREQ#	PROCESSOR BUS REQUEST	0	Processor bus request signal. When the CPU requires accessing an external bus The PBREQ# signal is asserted to issue a processor bus request to the external bus master when the CPU requires accessing an external bus (when it requires external access after a cache miss) while the CPU has relinquished bus access permission.

(Continued)

Symbol	Pin name	I/O	Function
OVF#	TIMER OVER- FLOW	0	Timer overflow signal. This pin outputs the "L" pulse when the timer reaches 0 after starting counting according to the settings in the DRAM Refresh Timer Register and DRAM Refresh Timer Pre-load Register with the TIMER ON/OFF bit in the System Support Control Register (SSCR) set to "1" The pulse width is the 1-clock width of the external bus clock when bit 31 in the DRAM Refresh Timer Pre-load Register is "0". When the bit is "1", the pulse width is the 3-clock width. The timer performs counting based on the external bus clock. Although this pin is used usually for the DRAM refresh request signal, it can be connected to the interrupt input (IRQx) of the interrupt control- ler (IRC) when the pulse width has been specified as the 3-clock width.
SAMEPAGE#	SAME PAGE DETECT	0	Same-page detection output pin. When the Same-Page Enable bit in the System Support Control Reg- ister (SSCR) has been "1", this pin outputs the "L" level if the CS4# pin is at the "L" level and if the address masked by the Same-Page Mask Register (SPGMR) matches the previously accessed address when compared. The SAMEPAGE# signal remains output during the bus cycle.
FLOAT#	FLOATING	I	Pin float input. Fixing this pin at the "L" level puts all of the output pins and bidirectional pins to the High-Z state.

• State of pins

Pin symbol	At reset	At bus grant			
ADR<27:2>	O (X)	I (D)			
AS#	O (H)	I (Z)			
BE0#	O (X)	O (Z)			
BE2#	O (X)	I (Z)			
CS0# to CS5#	O (H)	O (V)			
ERROR#	O (H)	O (V)			
LOCK#	O (H)	O (Z)			
PDOWN#	O (H)	O (H)			
PBREQ#	O (H)	O (V)			
SAMEPAGE#	O (H)	O (V)			

Pin symbol	At reset	At bus grant
D<31:0>	I (Z)	I (Z)
RDWR#	O (H)	I (Z)
BE1#	O (X)	O (Z)
BE3#	O (X)	O (Z)
BGRNT#	O (H)	O (L)
ASI<3:0>	O (X)	I (Z)
RDYOUT#	O (V)	O (V)
BMREQ#	O (H)	O (H)
OVF#	O (H)	O (V)

O (V) :The circuit is active with the output at a valid level.

O (X) :The circuit is inactive with the output indeterminate.

O (Z) :Output pins and High-Z.

- O (H) :The "H"level is output.
- O (L) :The "L" level is output.
- I (Z) :Input pins and High-Z
- I (D) :When the DRAM controller has been enabled, the pin is switched to serve as an output, from the clock cycle that follows the clock cycle in which the AS# pin becomes "L", and remains as the output until the ready signal input pin becomes "L". When the DRAM controller has been disabled, the pin enters the High-Z state.

2.	DRAM Controller	Related Pins	(MB86831/832/833/834/835)
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Symbol	Pin name	I/O	Function
RAS0# RAS1# RAS2# RAS3#	DRAM ROW ADDRESS STROBE	0	DRAM controller RAS outputs. The RAS0# to RAS3# signals are control signals corresponding to DRAM banks 0 to 3, respectively. The MB86833/835 does not support banks 1 to 3 because the RAS1# to RAS3# pins do not exist on the chip.
CAS0# CAS1# CAS2# CAS3#	DRAM COLUMN ADDRESS STROBE	0	DRAM CAS control outputs. For using the 32-bit bus width along with 2-CAS DRAM, the CAS0# to CAS3# pins are controlled in association with byte 0 (b31 to b24), byte 1 (b23 to b16), byte 2 (b15 to b8), and byte 3 (b7 to b0), respectively. For using the 16-bit bus width along with 2-CAS DRAM, the CAS2# and CAS3# pins correspond to byte 0 (byte data at an even-numbered ad- dress) and byte 1 (byte data at an odd-numbered address), respective- ly. When the 16-bit bus width is used, the outputs from the CAS0# and CAS1# pins are unpredictable. When 2-WE DRAM is used, the CAS0# to CAS3# pins provide the same output.
DWE0# DWE1# DWE2# DWE3#	DRAM WRITE ENABLE	ο	DRAM write enable control outputs. For using 2-WE DRAM, the DWE0# to DWE3# signals are controlled in association with byte 0 (b31 to b24), byte 1 (b23 to b16), byte 2 (b15 to b8), and byte 3 (b7 to b0), respectively. When 2-CAS DRAM is used, the DWE0# to DWE3# pins provide the same output. The DWE1# to DWE3# pins do not exist on the MB86833/835.
DOE#	DRAM OUTPUT	0	DRAM OE control output. When fast-page DRAM is used, the DRAM can be controlled without using the DOE# signal because the DWEx# and CASx# pins are con- trolled at the early write timing. When EDO (hyper page mode) DRAM is used, the DOE# signal is required for high-impedance control of the DRAM output.
ADR<13:2>	ADDRESS BUS	I/O	DRAM address signal. The DRAM controller outputs the multiplexed row and column address- es to a CPU address pin of ADR<13:2>.

• State of pins

Pin symbol	At reset	At bus grant
RAS3# to RAS0#	O (H)	O (V)
DOE#	O (H)	O (V)

Pin symbol	At reset	At bus grant
CAS3# to CAS0#	O (H)	O (V)
ADR<13:2>	O (X)	I (D)

O (V) : The circuit is active with the output at a valid level.

O (X) : The circuit is inactive with the output indeterminate.

O (H) : The "H" level is output.

I (D) : When the DRAM controller has been enabled, the pin is switched to serve as an output, from the clock cycle that follows the clock cycle in which the AS# pin becomes "L", and remains as the output until the ready signal input pin becomes "L". When the DRAM controller has been disabled, the pin enters the High-Z state.

3. Interrupt controller (IRC) Related Pins

Symbol	Pin name	I/O	Function
IRQ15/IRL3 IRQ14/IRL2 IRQ13/IRL1 IRQ12/IRL0 IRQ11 IRQ10 IRQ9 IRQ8	INTERRUPT REQUEST	1	Interrupt input pins. When the active level set for the interrupt controller (IRC) trigger mode is input to these pins, the request sense register of the interrupt control- ler (IRC) holds the interrupt request. (The interrupt controller (IRC) evaluates priority levels and performs coding for the IRL<3:0> pin, and notifies the CPU core of the interrupt level.) The IRQ15 to IRQ12 signals are assigned to the IRL<3:0> pin. They function as IRQ15 to IRQ12 when the interrupt controller (IRC) be- comes enabled.

4. Signals for the general-purpose 16-bit timer (MB86836)

Symbol	Pin name	I/O	Function
PRSCK0	Prescaler Clock Output0	0	Prescaler output pin. The external clock mode is not supported, which is included in the functions of the prescaler on the MB86942. The pin is reset to "L".
Ουτο	Timer Output0	0	Timer output pin. The external clock mode is not supported, which is included in the functions of the timer on the MB86942. The pin is reset to "L".
INO	Timer Input0	I	Timer count operation control pin. This pin inputs the GATE signal in MODE0 to MODE3 and the external trigger signal in MODE4.This pin has an internal pull-down resistor.

• Pin status

Symbol	Reset	Bus granted
PRSCK0	O (L)	O (V)
OUT0	O (L)	O (V)

Note : O (L) : Output "L" level

O (V) : Circuit activated ; effective level is output

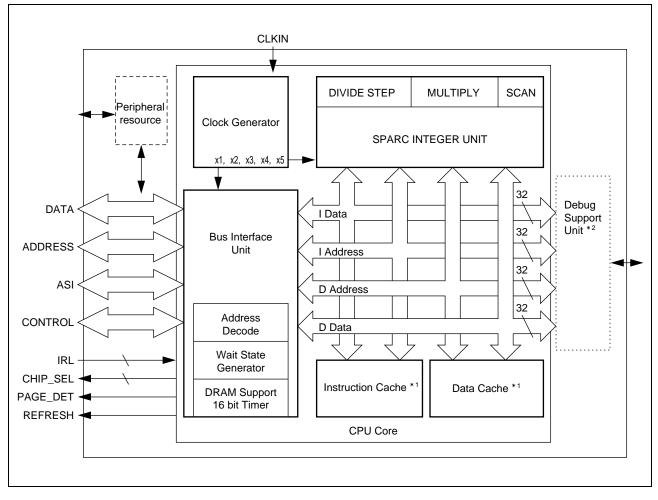
5. DDSU (Debug Support Unit) Related Pins (MB86832/834)

Symbol	Pin name	I/O	Function
EMUBRK#	Emulator Break	I	Emulator Break pin. When a reset is canceled, the EMUBRK# signal level is input to set a mode in combination with the EMUENG# signal level. The MB86832 contains a pull-up resistor (about 50 k Ω). Leave this pin open when the DSU (debug support unit) is not used. The MB86834 has no pull-up resistor.
EMUENB#	Emulator Enable	I/O	Emulator Enable pin. When a reset is canceled, the EMUENB# signal level is input to set a mode in combination with the EMUBRK# signal level. When a reset is canceled, this pin becomes an output pin after four clock cycles if either (DSUBRK# = DSUENB# = "L") or (DSUBRK# = "H", DSUENB# = "L") is set. The MB86832 contains a pull-up resistor (about 50 k Ω). Leave this pin open when the DSU (debug support unit) is not used. The MB86834 has no pull-up resistor.
EMUD<3:0>	Emulator Data Bus	I/O	Emulator Data pin. This pin outputs traced instruction addresses divided into eight compo- nents in the monitor mode. It also inputs instruction codes and outputs instruction or data addresses in the DSU mode. Since this pin serves as an output with the DSU disabled, leave the pin open if the DSU (debug support unit) is not to be used.
EMUSD<3:0>	Emulator Status/ Data Bus	I/O	Emulator Status/Data pin. This pin outputs the CPU status in the monitor mode and. It also inputs instruction codes and outputs instruction or data addresses in the DSU mode. Since this pin serves as an output with the DSU disabled, leave the pin open if the DSU (debug support unit) is not to be used.

6. Signals for the JTAG Test Port (MB86836)

Symbol	Pin name	I/O	Function
тск	Test Clock	I	JTAG test clock input pin. This pin has an internal pull-down resistor.
TMS	Test Mode	I	JTAG test mode selection pin. This pin has an internal pull-down resistor.
трі	Test Data In	I	JTAG test data input pin. This pin has an internal pull-down resistor.
TDO	Test Data Out	0	JTAG test data output pin.
TRST#	Test Reset	Ι	JTAG test reset pin. This pin is reset to "L". It has an internal pull-down resistor.

■ BLOCK DIAGRAM



*1:The cache capacity is as follows.

Parts number Item	MB86831	MB86832	MB86833	MB86834	MB86835	MB86836
Instruction cash	4 KB/2 way	8 KB/2 way	1 KB/Direct	16 KB/2 way	4 KB/2 way	8 KB/2 way
Data cash	2 KB/2 way	8 KB/2 way	1 KB/Direct	16 KB/2 way	2 KB/2 way	8 KB/2 way

*2:DSU (debug support unit) is added with MB86832/834.

■ ELECTRIC CHARACTERISTICS

1. ABSOLUTE MAXIMUM RATINGS

(1)MB86831-66/MB86832-66/MB86833

				(Vss = 0.0 V)
Parameter	Symbol	Rat	Unit	
Farameter	Symbol	Min.	Max.	
Power supply voltage(I/O)	Vdd5	- 0.5	6	V
Power supply voltage(Internal)	V _{DD3}	- 0.5	4	V
Input voltage	Vi	- 0.5	Vdd5 + 0.5	V
Storage temperature	Тѕтс	- 55	+ 125	°C
Temperature at bias	TBIAS	0	+ 70	°C
Overshoot	—	Within VDD5 + 1.0	V (Within 50 ns)	—
Undershoot	—	Within Vss – 1.0	V (Within 50 ns)	

(2)MB86834-108,-120/MB86836-90,-108

(_)	,			(Vss = 0.0 V)
Parameter	Symbol	Rat	ting	- Unit
	Symbol	Min.	Max.	Onic
Power supply voltage(I/O)	Vdd5(Vdde)	- 0.5	4.0	V
Power supply voltage(Internal)	Vdd3(Vddi)	- 0.5	3.0	V
Input voltage	VI	- 0.5	Vdde + 0.5	V
Storage temperature	Тѕтс	- 55	+ 125	°C
Temperature at bias	TBIAS	0	+ 70	°C

(3)MB86835

(Vss = 0.0 V)

Parameter	Symbol	Rat	Unit	
Farameter	Symbol	Min.	Max.	
Power supply voltage(I/O)	Vdd5	- 0.5	4	V
Power supply voltage(Internal)	V _{DD3}	- 0.5	4	V
Input voltage	Vı	- 0.5	Vdd5 + 0.5	V
Storage temperature	Тѕтс	- 55	+ 125	°C
Temperature at bias	TBIAS	0	+ 70	°C
Overshoot	_	Within V_{DD5} + 1.0 V (Within 50 ns)		—
Undershoot	—	Within Vss – 1.0	V (Within 50 ns)	—

(Notes on Board Wiring)

- For connecting the power supply and ground (GND), use multiple V_{DD} and V_{SS} pins. The system board based on the MB86830 series must be a multilayer board containing power supply (V_{DD}) and GND (V_{SS}) layers for stable power supply. Leave any pin designated as "N.C." unconnected.
- Insert sufficient decoupling capacitors near the MB86830 series. Changes to the output levels of many of the output pins on the MB86830 series (in particular, those with large load capacitance) may cause variation in power supply.
- For those systems which run at a high frequency, low-inductance capacitors and mutual wiring are recommended. Inductance can be lowered by shortening the distance between the processor and decoupling capacitor.
- For system reliability, the pin entering the tristate when the MB86830 series enters the bus grant state should be driven by a bus master. In particular, the LOCK#, ADR<27:2>, ASI<3:0> (ASI<3:0>/ADR<28:31>, ASI<3:0> /ADR<24:27>), BE0# to BE3#, D<31:0>, AS#, and RDWR# pins must be driven by other bus masters. Usually, these pins require no external pull-up resistor because they are driven by the processor when the processor is active or idle.
- WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current,temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

2. RECOMMENDED OPERATING CONDITIONS

(1)MB86831-66/MB86832-66/MB86833

(1)					(Vss = 0.0 V)
Parameter	Symbol		Value		l Init
Farameter	Symbol	Min.	Тур.	Max.	Unit
Power supply voltage $(I/O = 5.0 V)$	Vdd5	4.75	5.0	5.25	V
Power supply voltage $(I/O = 3.3 V)$	Vdd5	3.0	3.3	3.6	V
Power supply voltage (internal)	Vdd3	3.0	3.3	3.6	V
"L" level input voltage	VIL	0		$V_{\text{DD3}} imes 0.25$	V
"H" level input voltage	Vih	$V_{\text{DD3}} \times 0.65$		Vdd5	V
Operating temperature	Topr	0	+ 25	+ 70	°C

(2)MB86831-80/MB86832- 80, -100

(_)00001 0000002 00, 100					(Vss = 0.0 V)
Parameter	Symbol	Value			L lus it
Farameter	Symbol	Min.	Тур.	Max.	Unit
Power supply voltage $(I/O = 5.0 V)$	V _{DD5}	4.75	5.0	5.25	V
Power supply voltage $(I/O = 3.3 V)$	V _{DD5}	3.15	3.3	3.45	V
Power supply voltage (internal)	V _{DD3}	3.15	3.3	3.45	V
"L" level input voltage	VIL	0		$V_{DD3} imes 0.25$	V
"H" level input voltage	Vih	$V_{\text{DD3}} \times 0.65$	—	Vdd5	V
Operating temperature	Topr	0	+ 25	+ 70	°C

(3)MB86834-108,-120/MB86836-90,-108

(0)					(Vss = 0.0 V)
Parameter	Symbol		Value		Unit
Farameter	Symbol	Min.	Тур.	Max.	Unit
Power supply voltage (I/O)	Vdd5(Vdde)	3.15	3.3	3.45	V
Power supply voltage (internal)	Vdd3(Vdde)	2.4	2.5	2.6	V
"L" level input voltage	VIL	- 0.3	_	0.8	V
"H" level input voltage	Vін	2.0		Vdde + 0.3	V
Operating temperature	Topr	0	+ 25	+ 70	°C

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(4)MB86835

					(Vss = 0.0 V)
Parameter	Symbol		Value		Unit
Farameter	Symbol	Min.	Тур.	Max.	Unit
Power supply voltage $(I/O = 3.3 V)$	Vdd5	3.15	3.3	3.45	V
Power supply voltage (internal)	Vdd3	3.15	3.3	3.45	V
"L" level input voltage	VIL	0		$V_{\text{DD3}} imes 0.25$	V
"H" level input voltage	VIH	$V_{\text{DD3}} \times 0.65$		Vdd5	V
Operating temperature	Topr	0	+ 25	+ 70	°C

• The MB86831/832/833 can be used with a 5.0-V or 3.3-V interface.

5.0-V interface: $V_{DD5} = 5.0 \text{ V}$, $V_{DD3} = 3.3 \text{ V}$ (two power supplies)

3.3-V interface: $V_{DD5} = V_{DD3} = 3.3 \text{ V}$ (single power supply)

- When the 3.3-V interface is used, all signals input to the MB86830 series must be 3.3 V because the MB86830 series cannot input 5.0-V signals with that interface.
- When the 5.0-V interface is used, the output fully swings at 5.0 V. Although the input is always defined by a 3.3-V power supply, it can also accept 3.3 V or more.
- When the 5.0-V interface is used, the MB86830 series requires two power supplies. Follow the procedures below to turn on and off these power supplies:
 - Power-on procedure: $V_{DD3} \rightarrow V_{DD5} \rightarrow signal$ Shutdown procedure: Signal $\rightarrow V_{DD5} \rightarrow V_{DD3}$
- The MB86834/836 requires two power supplies of VDDE (3.3-V system) and VDDI (2.5-V system). Follow the procedures below to turn on and off these power supplies:

Power-on procedure: $V_{DDI} \rightarrow V_{DDE} \rightarrow signal$

Shutdown procedure: Signal $\rightarrow V_{\text{DDE}} \rightarrow V_{\text{DDI}}$

- The MB86835 has two V_DD, V_DD3 and V_DD5. Connect each of them to a 3.3-V power supply.
- The MB86834/835/836 uses only a 3.3-V interface; they cannot accept 5-V signals.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

3. DC Characteristics

(1)MB86831-66 (Maximum internal operation frequency:66 MHz)

• 5.0 V interface

	(Vde	$05 = 5.0 \text{ V} \pm 5\%, \text{ Vdd}$	$_{3} = 3.3 \text{ V} \pm 0.3$	3 V, Vss = 0.0	0 V, T _A = 0 °C	to + 70 °C)
Parameter	Symbol	Condition		Value		Unit
	Symbol	Condition	Min.	Тур.	Max.	Unit
"L" level input voltage	VIL	—	0		$V_{\text{DD3}} \times 0.25$	V
"H" level input voltage	VIH		$V_{\text{DD3}} \times 0.65$		Vdd5	V
"L" level output voltage	Vol	lo∟ = 4 mA	0		0.4	V
"H" level output voltage	Vон	Iон = - 4 mA	Vdd5 - 0.5		Vdd5	V
Input leakage current	Iu	$V_{\text{IN}} = 0 \text{ or } V_{\text{DD5}}$	- 10		10	μΑ
Trial state output leakage current	lız	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10	_	10	μΑ
Power supply current (VDD5)	Idd	33 MHz No-load		40		mA
Power supply current (VDD3)	ldd	66 MHz	—	150	—	mA
At sleep power supply current(VDD3)	ISLEEP	66 MHz		15	—	mA
Capacity of pins	CPIN	$ V_{\text{DD5}} = V_1 = 0 $			16	pF

$(V_{DD5} = V_{DD3} = 3.3)$	3 V ± 0.3%. Vss =	= 0.0 V. T _A = 0 °C	to + 70 °C)
$(v_{DD3} - v_{DD3} - 0.)$	J V ± 0.070, V00 -	- 0.0 0, 1A - 0 0	(0 + 10 + 0)

Parameter	Symbol	Symbol Condition	Value			Unit
Falameter	Symbol	Condition	Min.	Тур.	Max.	Onit
"L" level input voltage	Vı∟		0		$V_{DD3} imes 0.25$	V
"H" level input voltage	Vін		$V_{\text{DD3}} \times 0.65$		Vdd5	V
"L" level output voltage	Vol	lo∟ = 2 mA	0		0.4	V
"H" level output voltage	Vон	Iон = - 2 mA	$V_{\text{DD5}} - 0.5$		Vdd5	V
Input leakage current	lu	$V_{\text{IN}} = 0 \text{ or } V_{\text{DD5}}$	- 10		10	μA
Trial state output leakage current	llz	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10		10	μA
Power supply current (VDD5)	ldd	33 MHz No-load		30		mA
Power supply current (VDD3)	ldd	66 MHz		150	—	mA
At sleep power supply current(VDD3)	ISLEEP	66 MHz	—	15	—	mA
Capacity of pins	CPIN	$ V_{DD5} = V_1 = 0 $ f = 1 MHz			16	pF

(2)MB86831-80 (Maximum internal operation frequency:80 MHz)

• 5.0 V interface

$(V_{DD5} = 5.0 \text{ V} \pm 5\%, \text{ V}_{DD3} = 3.3 \text{ V} \pm 0.15 \text{ V}, \text{ V}_{SS} = 0.0 \text{ V}, \text{ T}_{A} = 0 ^{\circ}\text{C} \text{ to}$	o + 70 °C)
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Parameter	Symbol	Condition	Value			Unit
Falameter	Symbol	Condition	Min.	Тур.	Max.	Unit
"L" level input voltage	VIL		0		$V_{\text{DD3}} \times 0.25$	V
"H" level input voltage	VIH		$V_{\text{DD3}} \times 0.65$		Vdd5	V
"L" level output voltage	Vol	lo∟ = 4 mA	0		0.4	V
"H" level output voltage	Vон	Iон = - 4 mA	$V_{\text{DD5}} - 0.5$		Vdd5	V
Input leakage current	lu	$V_{IN} = 0 \text{ or } V_{DD5}$	- 10		10	μA
Trial state output leakage current	ILZ	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10		10	μA
Power supply current (VDD5)	ldd	40MHz No-load		50		mA
Power supply current (VDD3)	ldd	80MHz	—	200	—	mA
At sleep power supply current(VDD3)	ISLEEP	80MHz		20	_	mA
Capacity of pins	CPIN	$ V_{\text{DD5}} = V_1 = 0 $	_		16	pF

$V_{DD5} = 5.0 V \pm 5\%$,	$V_{DD3} = 3.3 V \pm 0.15$	V, Vss = 0.0 V, T/	$A = 0 ^{\circ}C to + 70 ^{\circ}C$
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Parameter	Symbol	Condition	Value			Unit
Farameter	Symbol	Condition	Min.	Тур.	Max.	Onit
"L" level input voltage	VIL		0		$V_{\text{DD3}} \times 0.25$	V
"H" level input voltage	Vін		$V_{\text{DD3}} \times 0.65$		Vdd5	V
"L" level output voltage	Vol	IoL = 2 mA	0		0.4	V
"H" level output voltage	Vон	Іон = − 2 mA	Vdd5 - 0.5		Vdd5	V
Input leakage current	lu	$V_{\text{IN}} = 0 \text{ or } V_{\text{DD5}}$	- 10		10	μA
Trial state output leakage current	lız	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10		10	μΑ
Power supply current (VDD5)	Idd	40MHz No-load	—	36		mA
Power supply current (VDD3)	Idd	80MHz		200		mA
At sleep power supply current(VDD3)	ISLEEP	80MHz		20		mA
Capacity of pins	Сріл	$ V_{\text{DD5}} = V_1 = 0 $ f = 1 MHz			16	pF

(3)MB86832-66 (Maximum internal operation frequency:66 MHz)

• 5.0 V interface

$(V_{DD5} = 5.0 \text{ V} \pm 5\%, \text{ V}_{DD3} = 3.3 \text{ V} \pm 0.3 \text{ V}, \text{ V}_{SS} = 0.0 \text{ V}, \text{ T}_{A} = 0 ^{\circ}\text{C} \text{ to } + 70 ^{\circ}\text{C})$							
Parameter	Symbol	Symbol Condition	Value			Unit	
Falameter	Symbol		Min.	Тур.	Max.	Onit	
"L" level input voltage	VIL		0		$V_{DD3} imes 0.25$	V	
"H" level input voltage	Vін		$V_{\text{DD3}} \times 0.65$		Vdd5	V	
"L" level output voltage	Vol	lo∟ = 4 mA	0		0.4	V	
"H" level output voltage	Vон	Iон = - 4 mA	Vdd5 - 0.5		Vdd5	V	
Input leakage current	lu	$V_{IN} = 0 \text{ or } V_{DD5}$	- 10		10	μΑ	
Trial state output leakage current	ILZ	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10	—	10	μΑ	
Power supply current (VDD5)	ldd	33 MHz No-load		40	—	mA	
Power supply current (VDD3)	ldd	66 MHz	—	200	—	mA	
At sleep power supply current(VDD3)	ISLEEP	66 MHz	_	15	—	mA	
Capacity of pins	CPIN	$ V_{\text{DD5}} = V_1 = 0 $			16	pF	

• 3.3 V interface

$(V_{DD5} = V_{DD3} = 3.3 \text{ V} \pm 0.3 \text{ V}, \text{ Vss} = 0.0 \text{ V}, \text{ T}_{A} = 0 \text{ }^{\circ}\text{C} \text{ to } + 70 \text{ }^{\circ}\text{C})$

Parameter	Symbol Condition	Value			Unit	
Farameter	Symbol	Condition	Min.	Тур.	Max.	Unit
"L" level input voltage	Vil		0		$V_{DD3} imes 0.25$	V
"H" level input voltage	Vін		$V_{DD3} imes 0.65$		Vdd5	V
"L" level output voltage	Vol	lo∟ = 2 mA	0		0.4	V
"H" level output voltage	Vон	Iон = - 2 mA	Vdd5 - 0.5		Vdd5	V
Input leakage current	Lu	$V_{IN} = 0 \text{ or } V_{DD5}$	- 10		10	μΑ
Trial state output leakage current	ILZ	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10	_	10	μA
Power supply current (VDD5)	Idd	33 MHz No-load	—	30	—	mA
Power supply current (VDD3)	Idd	66 MHz	—	200	—	mA
At sleep power supply current(VDD3)	ISLEEP	66 MHz	—	15	—	mA
Capacity of pins	CPIN	$ V_{\text{DD5}} = V_{\text{I}} = 0 $ f = 1 MHz			16	pF

(4)MB86832-80 (Maximum internal operation frequency:80 MHz)

• 5.0 V interface

Parameter	Symbol	Condition		Value		Unit
Falameter	Symbol	Condition	Min.	Тур.	Max.	
"L" level input voltage	VIL		0		$V_{DD3} imes 0.25$	V
"H" level input voltage	VIH		$V_{\text{DD3}} \times 0.65$		Vdd5	V
"L" level output voltage	Vol	lo∟ = 4 mA	0		0.4	V
"H" level output voltage	Vон	Iон = -4 mA	$V_{\text{DD5}} - 0.5$		Vdd5	V
Input leakage current	Iu	$V_{IN} = 0 \text{ or } V_{DD5}$	- 10		10	μΑ
Trial state output leakage current	lız	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10		10	μΑ
Power supply current (VDD5)	Idd	40MHz No-load		50	—	mA
Power supply current (VDD3)	Idd	80MHz		250	—	mA
At sleep power supply current(VDD3)	ISLEEP	80MHz		20	—	mA
Capacity of pins	CPIN	$ V_{\text{DD5}} = V_1 = 0 $ f = 1 MHz			16	pF

Parameter	Symbol	Condition	ndition		Value		
Falameter	Symbol	Condition	Min.	Тур.	Max.	Unit	
"L" level input voltage	VIL		0		$V_{\text{DD3}} \times 0.25$	V	
"H" level input voltage	Vін		$V_{\text{DD3}} \times 0.65$		Vdd5	V	
"L" level output voltage	Vol	lo∟ = 2 mA	0		0.4	V	
"H" level output voltage	Vон	Iон = - 2 mA	Vdd5 - 0.5		Vdd5	V	
Input leakage current	lu	$V_{\text{IN}} = 0 \text{ or } V_{\text{DD5}}$	- 10		10	μA	
Trial state output leakage current	lız	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10		10	μΑ	
Power supply current (VDD5)	ldd	40MHz No-load	—	36		mA	
Power supply current (VDD3)	ldd	80MHz		250		mA	
At sleep power supply current(VDD3)	ISLEEP	80MHz	—	20	_	mA	
Capacity of pins	CPIN	$V_{DD5} = V_I = 0$ f = 1 MHz	—		16	pF	

(5)MB86832-100 (Maximum internal operation frequency:100 MHz)

• 5.0 V interface

$(V_{DD5} = 5.0 \text{ V} \pm 5\%, \text{ V}_{DD3} = 3.3 \text{ V} \pm 0.15 \text{ V}, \text{ V}_{SS} = 0.0 \text{ V}, \text{ T}_{A} = 0 ^{\circ}\text{C} \text{ to } + 7 ^{\circ}\text{C} ^{\circ}\text{C} \text{ to } + 7 ^{\circ}\text{C} ^{\circ}\text{C} ^{\circ}\text{C} ^{\circ}\text{C} \text{ to } + 7 ^{\circ}\text{C} $	0 °C)
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Parameter	Symbol	Condition	Condition		Value		
Farameter	Symbol	Condition	Min.	Тур.	Max.	Unit	
"L" level input voltage	VIL		0		$V_{DD3} imes 0.25$	V	
"H" level input voltage	Vін		$V_{\text{DD3}} \times 0.65$		Vdd5	V	
"L" level output voltage	Vol	IoL = 4 mA	0		0.4	V	
"H" level output voltage	Vон	$I_{OH} = -4 \text{ mA}$	$V_{\text{DD5}} - 0.5$		V _{DD5}	V	
Input leakage current	Iu	$V_{\text{IN}} = 0 \text{ or } V_{\text{DD5}}$	- 10		10	μA	
Trial state output leakage current	ILZ	$V_{\text{OUT}} = 0 \text{ or } V_{\text{DD5}}$	- 10		10	μΑ	
Power supply current (VDD5)	ldd	33MHz No-load		40		mA	
Power supply current (VDD3)	ldd	100MHz		300		mA	
At sleep power supply current(VDD3)	ISLEEP	100MHz		25	_	mA	
Capacity of pins	CPIN	$V_{DD5} = V_I = 0$ f = 1 MHz			16	pF	

$(V_{DD5} = V_{DD3} = 3.3 \text{ V} \pm 0.15 \text{ V}, \text{ Vss} = 0.0 \text{ V}, \text{ T}_{A} = 0 ^{\circ}\text{C} \text{ to } + 7.0 ^{\circ}\text{C} ^{\circ}\text{C} \text{ to } + 7.0 ^{\circ}\text{C} ^{\circ}\text{C} \text{ to } + 7.0 ^{\circ}\text{C} ^{$	70 °C)
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Parameter	Symbol	Condition	Value			Unit
Falameter	Symbol	Condition	Min.	Тур.	Max.	Unit
"L" level input voltage	VIL		0		$V_{DD3} imes 0.25$	V
"H" level input voltage	Vін		$V_{\text{DD3}} \times 0.65$		Vdd5	V
"L" level output voltage	Vol	IoL = 2 mA	0		0.4	V
"H" level output voltage	Vон	Іон = − 2 mA	Vdd5 - 0.5		Vdd5	V
Input leakage current	Li	$V_{\text{IN}} = 0 \text{ or } V_{\text{DD5}}$	- 10		10	μA
Trial state output leakage current	lız	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10		10	μΑ
Power supply current (VDD5)	Idd	33MHz No-load	—	30		mA
Power supply current (VDD3)	ldd	100MHz		300		mA
At sleep power supply current(VDD3)	ISLEEP	100MHz		25	—	mA
Capacity of pins	Сріл	$ V_{\text{DD5}} = V_1 = 0 $ f = 1 MHz			16	pF

(6)MB86833 (Maximum internal operation frequency:66 MHz)

• 5.0 V interface

Parameter	Symbol	Condition	Value			Unit
Farameter	Symbol	Condition	Min.	Тур.	Max.	Onit
"L" level input voltage	VIL		0		$V_{DD3} imes 0.25$	V
"H" level input voltage	VIH		$V_{\text{DD3}} \times 0.65$		Vdd5	V
"L" level output voltage	Vol	lo∟ = 4 mA	0		0.4	V
"H" level output voltage	Vон	Iон = -4 mA	Vdds - 0.5		V _{DD5}	V
Input leakage current	lu	$V_{\text{IN}} = 0 \text{ or } V_{\text{DD5}}$	- 10		10	μΑ
Trial state output leakage current	lız	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10		10	μA
Power supply current (VDD5)	ldd	33 MHz No-load		40		mA
Power supply current (VDD3)	Idd	66 MHz		120		mA
At sleep power supply current(VDD3)	ISLEEP	66 MHz		15	_	mA
Capacity of pins	CPIN	$ V_{\text{DD5}} = V_1 = 0 $ f = 1 MHz			16	pF

Parameter	Symbol	Condition	Value			Unit
Falameter	Symbol		Min.	Тур.	Max.	Unit
"L" level input voltage	VIL		0		$V_{DD3} imes 0.25$	V
"H" level input voltage	Vін		$V_{DD3} imes 0.65$		Vdd5	V
"L" level output voltage	Vol	IoL = 2 mA	0		0.4	V
"H" level output voltage	Vон	Іон = − 2 mA	Vdd5 - 0.5		Vdd5	V
Input leakage current	lu	$V_{IN} = 0 \text{ or } V_{DD5}$	- 10		10	μA
Trial state output leakage current	ILZ	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10		10	μΑ
Power supply current (VDD5)	ldd	33 MHz No-load		30		mA
Power supply current (VDD3)	Idd	66 MHz		120		mA
At sleep power supply current(VDD3)	ISLEEP	66 MHz	_	15	—	mA
Capacity of pins	Срім	$ V_{\text{DD5}} = V_1 = 0 $ f = 1 MHz	_		16	pF

(7)MB86834-108 (Maximum internal operation frequency:108 MHz)

	(Vdd5 =	$3.3 \text{ V} \pm 0.15 \text{ V}, \text{ Vdc}$	$a = 2.5 V \pm 0.$	1 V, Vss = 0.0	0 V, T _A = 0 °C	to + 70 °C)
Parameter	Symbol	Condition	Value			Unit
Faiameter	Symbol	Condition	Min.	Тур.	Max.	Onic
"L" level input voltage	Vı∟	—	0	—	0.8	V
"H" level input voltage	Vін		2.0	_	Vdde	V
"L" level output voltage	Vol	IoL = 2.0mA	0		0.4	V
"H" level output voltage	Vон	Іон = - 2.0mA	Vdde - 0.4	_	Vdde	V
Input leakage current	lu	$V_{\text{IN}} = 0 \text{ or } V_{\text{DDE}}$	- 5	_	5	μA
Trial state output leakage current	ILZ	$V_{OUT} = 0 \text{ or } V_{DDE}$	- 5	_	5	μΑ
Power supply current (VDD5)	Idd	33 MHz No-load	—	30		mA
Power supply current (VDD3)	Idd	108 MHz	—	250		mA
At sleep power supply current(VDD3)	ISLEEP	108 MHz		20		mA
Capacity of pins	Cpin	$V_{DDE} = V_I = 0$ f = 1 MHz			16	pF

(8)MB86834-120 (Maximum internal operation frequency:120 MHz)
 $(V_{DD5} = 3.3 V \pm 0.15 V, V_{DD3} = 2.5 V \pm 0.1 V, V_{SS} = 0.0 V, T_A = 0 °C to + 70 °C)$ ParameterSymbolConditionValueUnit

Parameter	Symbol Condition				Unit	
Falameter	Symbol	Condition	Min.	Тур.	Max.	Unit
"L" level input voltage	VIL	—	0		0.8	V
"H" level input voltage	Vін		2.0	_	Vdde	V
"L" level output voltage	Vol	IoL = 2.0mA	0	_	0.4	V
"H" level output voltage	Vон	Іон = - 2.0mA	$V_{\text{DDE}} - 0.4$	_	Vdde	V
Input leakage current	lu	$V_{\text{IN}} = 0 \text{ or } V_{\text{DDE}}$	- 5	_	5	μΑ
Trial state output leakage current	lız	$V_{OUT} = 0 \text{ or } V_{DDE}$	- 5		5	μA
Power supply current (VDD5)	Idd	40 MHz No-load		36		mA
Power supply current (VDD3)	ldd	120 MHz		280	_	mA
At sleep power supply current(VDD3)	ISLEEP	120 MHz	_	23		mA
Capacity of pins	CPIN	$V_{DDE} = V_I = 0$ f = 1 MHz		_	16	pF

Parameter	0	Condition		Value		11
	Symbol		Min.	Тур.	Max.	Unit
"L" level input voltage	VIL		0		$V_{DD3} imes 0.25$	V
"H" level input voltage	Vін		$V_{DD3} imes 0.65$		Vdd5	V
"L" level output voltage	Vol	IoL = 2 mA	0		0.4	V
"H" level output voltage	Vон	Iон = - 2 mA	Vdd5 - 0.5		Vdd5	V
Input leakage current	Lu	$V_{IN} = 0 \text{ or } V_{DD5}$	- 10		10	μΑ
Trial state output leakage current	ILZ	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 10		10	μA
Power supply current (VDD5 + VDD3)	Idd	84 MHz No-load	_	200	_	mA
At sleep power supply current (VDD3)	ISLEEP	84 MHz	_	20	—	mA
Capacity of pins	CPIN	$V_{DD5} = V_I = 0$ f = 1 MHz	_		16	pF

(10)MB86836-90 (Maximum internal operation frequency:90 MHz) $(V_{DD5} = 3.3 \text{ V} \pm 0.15 \text{ V}, V_{DD3} = 2.5 \text{ V} \pm 0.1 \text{ V}, \text{ Vss} = 0.0 \text{ V}, \text{ T}_{A} = 0 \text{ °C tc}$

$(V_{DD5} = 3.3 \text{ V} \pm 0.15 \text{ V}, V_{DD3} = 2.5 \text{ V} \pm 0.1 \text{ V}, \text{ Vss} = 0.0 \text{ V}, \text{ T}_{A} = 0 \text{ °C to } + 70 \text{ °C})$								
Parameter	Symbol	Condition		Unit				
Falanetei	Symbol	Condition	Min.	Тур.	Max.	Onic		
"L" level input voltage	VIL		0		0.8	V		
"H" level input voltage	Vін		2.0	_	Vdd5	V		
"L" level output voltage	Vol	IoL = 2 mA	0		0.4	V		
"H" level output voltage	Vон	Іон = − 2 mA	Vdd5 - 0.4		Vdd5	V		
Input leakage current	lu	$V_{IN} = 0 \text{ or } V_{DD5}$	- 5		5	μΑ		
Trial state output leakage current	llz	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 5		5	μΑ		
Power supply current (V _{DD5} = 3.3 V)	IDD	40 MHz No-load		36		mA		
Power supply current (V _{DD3} = 2.5 V)	IDD	90 MHz		180		mA		
At sleep power supply current	ISLEEP	90 MHz		17		mA		
Capacity of pins	CPIN	$ V_{\text{DD5}} = V_1 = 0 $ f = 1 MHz			16	pF		

(11)MB86836-108 (Maximum internal operation frequency:108 MHz)

$(V_{DD5} = 3.3 \text{ V} \pm 0.15 \text{ V}, V_{DD3} = 2.5 \text{ V} \pm 0.1 \text{ V}, V_{SS} = 0.0 \text{ V}, T_A = 0 ^{\circ}\text{C} \text{ to } + 70 ^{\circ}\text{C})$								
Parameter	Symbol	Condition		Unit				
Farameter	Symbol		Min.	Тур.	Max.	Unit		
"L" level input voltage	VIL		0		0.8	V		
"H" level input voltage	Vін		2.0	_	Vdd5	V		
"L" level output voltage	Vol	IoL = 2 mA	0		0.4	V		
"H" level output voltage	Vон	Іон = − 2 mA	Vdd5 - 0.4		Vdd5	V		
Input leakage current	lu	$V_{IN} = 0 \text{ or } V_{DD5}$	- 5	_	5	μA		
Trial state output leakage current	llz	$V_{OUT} = 0 \text{ or } V_{DD5}$	- 5	_	5	μΑ		
Power supply current (V _{DD5} = 3.3 V)	IDD	40 MHz No-load		36		mA		
Power supply current (V _{DD3} = 2.5 V)	IDD	108 MHz		200		mA		
At sleep power supply current	ISLEEP	108 MHz		20		mA		
Capacity of pins	CPIN	$ V_{\text{DD5}} = V_1 = 0 $ f = 1 MHz			16	pF		

4. AC Characteristics

All are provided by CLKIN (BUS clock), and the AC characteristic does not depend on the frequency of the operation in CPU.

(1)MB86831-66/MB86832-66/MB86833 (Maximum internal operation frequency:66 MHz)

	Parameter		/bb3 = 3.3 V ± 0.3 V, Vss = 0.0 V, T _A = 0 °C to + Value				
Classifica- tion		Symbol	V DD5 = 5	.0 V ± 5%	VDD5 = 3.3	Unit	
tion			Min.	Max.	Min.	Max.	1
	CLKIN cycle time		30	100	30	100	ns
	CLKIN high time		10		10		ns
CLK	CLKIN low time		10		10		ns
	CLKIN rising time		—	3		3	ns
	CLKIN falling time		—	3		3	ns
	Delay time	D 04 0		20		20	ns
	Hold time	– D<31:0>	2	—	2		ns
	Delay time		—	20		21	ns
	Hold time		2	—	2		ns
	Delay time			20		21	ns
	Hold time	BE0# to BE3#	2		2		ns
	Delay time	– ASI<3:0>		20		21	ns
	Hold time		2		2		ns
	Delay time	- CS0# to CS5#		20		21	ns
	Hold time		2	—	2		ns
	Delay time			20		21	ns
	Hold time	- SAMEPAGE#	2		2		ns
• • •	Delay time			18		19	ns
Output	Hold time	– RDWR#	2	—	2		ns
	Delay time			18		19	ns
	Hold time	LOCK#	2	—	2		ns
	Delay time	10"		18		19	ns
	Hold time	AS#	2		2		ns
	Delay time	0)/5//		20		21	ns
	Hold time	OVF#	2		2		ns
	Delay time		—	18		19	ns
	Hold time	BGRNT#	2		2		ns
	Delay time		—	18		19	ns
	Hold time	– PBREQ#	2		2	—	ns
	Delay time		—	18		19	ns
	Hold time	BMREQ#	2		2	<u> </u>	ns

(Continued)

(V	$DD3 = 3.3 \text{ V} \pm 0.3 \text{ V}$, $Vss = 0.0 \text{ V}$, $T_A = 0 ^{\circ}C$ to	+ 70 °C)

	Parameter		Value				
Classifica- tion		Symbol	$V_{\text{DD5}} = 5.0 \text{ V} \pm 5\%$		$V_{\text{DD5}} = \textbf{3.3 V} \pm \textbf{0.3 V}$		Unit
			Min.	Max.	Min.	Max.	
	Delay time	RDYOUT#		20	—	21	ns
	Hold time	(Internal ready mode)	2	_	2	_	ns
	Delay time	RDYOUT# *	—	15	—	15	ns
Output	Hold time	(External ready mode)	2	_	2		ns
	Delay time	ERROR#		20	—	21	ns
	Hold time		2		2		ns
	Delay time	PDOWN#		20		21	ns
	Hold time	1 00000#	2		2		ns
	Setup time	READY#	14		14		ns
	Hold time		2	_	2		ns
	Setup time	MEXC#	14		14		ns
	Hold time	- WEAC#	2	—	2		ns
	Setup time	– D<31:0>	14	_	14	—	ns
	Hold time		2	—	2		ns
Input	Setup time	– BREQ#	12	—	12		ns
mput	Hold time		2	_	2	—	ns
	Setup time	BMACK#	12	_	12	—	ns
	Hold time	DIVIACIN#	2	_	2	—	ns
	Setup time	IRL<3:0>	Asynchronous		Asynchronous		ns
	Hold time		Asynchronous		Asynchronous		ns
	Setup time	WKUP#	Asynchronous		Asynchronous		ns
	Hold time	- VVNOF#	Asynchronous		Asynchronous		ns
	Setup time	RDWR#	12	_	12		ns
	Hold time		2	—	2		ns
	Setup time	AS#	12	—	12		ns
	Hold time	— A3#	2	—	2		ns
External	Input setup time	A SL 22:05	12		12		ns
bus master input	Hold time	— ASI<3:0>	2	_	2		ns
•	Setup time	ADR<27:2>	12		12		ns
	Hold time	- AUK<21.2>	2	—	2	—	ns
	Setup time	BE0#	12		12		ns
	Hold time	BE2#	2	_	2		ns

(Continued)

		(v	DD3 = 3.3 V		$s = 0.0 V, T_A$	$= 0 $ $^{\circ}$ $C $ to $-$	⊦70 °C)
Classifica-	Parameter	Symbol	Value				
tion			$V_{DD5} = 5.$	$V_{DD5} = 5.0 V \pm 5\%$		$V_{DD5} = 3.3 V \pm 0.3 V$	
			Min.	Max.	Min.	Max.	
DRAMC output	Delay time		—	15	—	15	ns
	Hold time	RAS0# to RAS3#	2		2	_	ns
	Delay time	CAS0# to CAS3#	—	15	—	15	ns
	Hold time		2		2		ns
	Delay time	DWE0# to DWE3#		15		15	ns
	Hold time		2		2		ns
	Delay time	DOE#		15		15	ns
	Hold time		2		2		ns
	Setup time	IRQ15 to IRQ8	Asynchronous		Asynchronous		ns
IRC input	Hold time		Asynch	ironous	Asynch	ronous	ns
	"H" level period		$2 \times P + 10$		$2 \times P + 10$		ns
	"L" level period		$2 \times P + 10$		$2 \times P + 10$		ns

P:Period (Cycle time)

*: RDYOUT# at the external ready mode is provided for from READY# input.

Notes

- Each parameter is valid within the specified ranges of temperatures and supply voltages unless otherwise noted.
- Each voltage value is based on the GND (Vss = 0.0 V) level. The timing measurement reference point is 1.5 V, the input level is 0.4 to 2.4 V, and the input rise time and fall time are 2 ns or less.
- Do not leave more than one output pins short-circuited for 1 second or more.
- The external output load capacitance is 30 pF.
- The specifications of pins other than those pins designated as asynchronous inputs and than the RDYOUT# pin in external ready mode are determined by the rising edge of the external clock (CLKIN).
- These specifications are subject to change for improvement.
- The reset period requires at least 4 CLKIN cycles. The PLL oscillation stabilization delay time requires at least 4000 clock (CLKIN) pulses. For 40-MHz (25 ns) clock input, for example, the reset signal must therefore be negated 100 μs later.

(2)MB86831-80/MB86832-80 (Maximum internal operation frequency:80 MHz)

				Va	alue		
Classifica- tion	Parameter	Symbol	VDD5 = 5	.0 V ± 5%	VDD5 = 3.3	V ± 0.15 V	Unit
tion			Min.	Max.	Min.	Max.	
	CLKIN cycle time		25	100	25	100	ns
	CLKIN high time	_	8	_	8		ns
CLK	CLKIN low time	_	8		8		ns
	CLKIN rising time			3		3	ns
	CLKIN falling time			3		3	ns
	Delay time	D 01 0		16		20	ns
	Hold time	— D<31:0>	2		2		ns
	Delay time	100.07.0		18		21	ns
	Hold time	- ADR<27:2>	2		2		ns
	Delay time			16		21	ns
	Hold time	— BE0# to BE3#	2	_	2		ns
	Delay time	101.0.0		16		21	ns
	Hold time		2		2		ns
	Delay time			16		21	ns
	Hold time	— CS0# to CS5#	2		2		ns
	Delay time			16		21	ns
	Hold time	- SAMEPAGE#	2	_	2		ns
	Delay time			14		19	ns
	Hold time	- RDWR#	2	_	2		ns
Output	Delay time	1.001//		14		19	ns
	Hold time	LUCK#	2	_	2		ns
	Delay time	A C #		14		19	ns
	Hold time	— A5#	2		2		ns
	Delay time	0)/5//		16		21	ns
	Hold time	– OVF#	2	_	2		ns
	Delay time			14		19	ns
	Hold time	— BGRNT#	2	—	2		ns
	Delay time			14		19	ns
	Hold time	– PBREQ#	2	—	2		ns
	Delay time		—	16	—	19	ns
	Hold time	BMREQ#	2		2		ns
	Delay time	RDYOUT#		16		21	ns
	Hold time	(Internal ready mode)	2		2		ns

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					alue		
Classifica-	Parameter	Symbol	V _{DD5} = 5 .	$V_{\text{DD5}} = 5.0 \text{ V} \pm 5\%$		$V \pm 0.15 V$	Unit
tion			Min.	Max.	Min.	Max.	
	Delay time	RDYOUT# *		14		15	ns
	Hold time	(External ready mode)	2	—	2		ns
Output	Delay time	EPPOP#		14		21	ns
•	Hold time		2		2	—	ns
	Delay time		—	14	—	21	ns
	Hold time		2		2	—	ns
	Setup time		10	—	10	—	ns
	Hold time	KEADT#	2	—	2	—	ns
	Setup time	MEXC#	10		10		ns
	Hold time		2	—	2	—	ns
	Setup time	(External ready	12		12		ns
	Hold time	D<31.0>	2		2		ns
loout	Setup time	DDEO#	10		10		ns
Input	Hold time		2		2		ns
	Setup time	PMACK#	10		10		ns
	Hold time	BIVIACK#	2	—	2	—	ns
	Setup time	IDI -2:05	Asynchronous		Asynchronous		ns
	Hold time	IKL<3.0>	Asyncl	nronous	Asynch	nronous	ns
	Setup time		Asynchronous		Asynchronous		ns
	Hold time		Asyncl	Asynchronous		nronous	ns
	Setup time	DDWD#	12		12		ns
	Hold time	- KDWK#	2		2		ns
	Setup time	AC#	12		12		ns
	Hold time	— A3#	2		2		ns
External	Input setup time		12	—	12	—	ns
bus master input	Hold time		2	—	2		ns
F • • •	Setup time	ADD -07:05	12		12	—	ns
	Hold time		2		2	—	ns
	Setup time	PE2#	12		12	—	ns
	Hold time		2		2		ns

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(Continued)

				,	lue		,
Classifica- tion	Parameter	Symbol	VDD5 = 5.	0 V ± 5%	$V_{\text{DD5}} = 3.3$	$V \pm 0.15 V$	Unit
			Min.	Max.	Min.	Max.	
	Delay time	RAS0# to RAS3#	—	12	—	15	ns
	Hold time		2	_	2	—	ns
	Delay time	CAS0# to CAS3#		12	—	15	ns
DRAMC output	Hold time	CA30# 10 CA35#	2		2	—	ns
	Delay time	DWE0# to DWE3# -	—	12	—	15	ns
	Hold time	DVVE0# 10 DVVE3#	2	_	2	_	ns
	Delay time	DOE#	—	12	—	15	ns
	Hold time	DOL#	2	_	2	—	ns
	Setup time		Asynch	nronous	Asynch	ironous	ns
IRC input	Hold time	IRQ15 to IRQ8	Asynch	nronous	Asynch	ironous	ns
into input	"H" level period		$2 \times P + 10$		$2 \times P + 10$	—	ns
	"L" level period]	$2 \times P + 10$		$2 \times P + 10$		ns

(V_{DD3} = 3.3 V \pm 0.15 V, Vss = 0.0 V, T_A = 0 °C to $\,+$ 70 °C)

P:Period (Cycle time)

* : RDYOUT# at the external ready mode is provided for from READY# input.

Notes

- Each parameter is valid within the specified ranges of temperatures and supply voltages unless otherwise noted.
- Each voltage value is based on the GND (Vss = 0.0 V) level. The timing measurement reference point is 1.5 V, the input level is 0.4 to 2.4 V, and the input rise time and fall time are 2 ns or less.
- Do not leave more than one output pins short-circuited for 1 second or more.
- The external output load capacitance is 30 pF.
- The specifications of pins other than those pins designated as asynchronous inputs and than the RDYOUT# pin in external ready mode are determined by the rising edge of the external clock (CLKIN).
- These specifications are subject to change for improvement.
- The reset period requires at least 4 CLKIN cycles. The PLL oscillation stabilization delay time requires at least 4000 clock (CLKIN) pulses. For 40-MHz (25 ns) clock input, for example, the reset signal must therefore be negated 100 μs later.

(3)MB86832-100 (Maximum internal operation frequency:100 MHz)

					alue	$x = 0 \circ C \text{ to } +$	
Classifica- tion	Parameter	Symbol	VDD5 = 5	.0 V ± 5%	VDD5 = 3.3	V ± 0.15 V	Unit
tion			Min.	Max.	Min.	Max.	
	CLKIN cycle time		25	100	25	100	ns
	CLKIN high time		10		10		ns
CLK	CLKIN low time	_	10		10		ns
	CLKIN rising time	_		3	_	3	ns
	CLKIN falling time			3		3	ns
	Delay time	D 04 0		16		20	ns
	Hold time	— D<31:0>	2	—	2	—	ns
	Delay time			18	_	21	ns
	Hold time	- ADR<27:2>	2		2		ns
	Delay time			16		21	ns
	Hold time	— BE0# to BE3#	2	—	2		ns
	Delay time			16	_	21	ns
	Hold time	— ASI<3:0>	2	—	2		ns
	Delay time	- BE0# to BE3# - ASI<3:0> - CS0# to CS5# - SAMEPAGE# - RDWR# - LOCK# -		16		21	ns
	Hold time	— CS0# to CS5#	2	—	2		ns
	Delay time			16		21	ns
	Hold time	- SAMEPAGE#	2	—	2		ns
	Delay time	- SAMEPAGE# -		14		19	ns
	Hold time	- RDWR#	2	—	2		ns
Output	Delay time			14		19	ns
	Hold time	LOCK#	2		2		ns
	Delay time	10//		14		19	ns
	Hold time	— AS#	2	—	2		ns
	Delay time	0)/5//		16	_	21	ns
	Hold time	OVF#	2		2		ns
	Delay time		_	14	_	19	ns
	Hold time	BGRNT#	2		2		ns
	Delay time			14	—	19	ns
	Hold time	– PBREQ#	2	—	2		ns
	Delay time			16	—	19	ns
	Hold time	BMREQ#	2	—	2	—	ns
	Delay time	RDYOUT#		16		21	ns
	Hold time	(Internal ready mode)	2		2		ns

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$(V_{DD3} = 3.3 \text{ V} \pm 0.15 \text{ V}, \text{ Vss} = 0.0 \text{ V}, \text{ T}_{A} = 0 ^{\circ}\text{C} \text{ to } + 70 ^{\circ}\text{C})$	$(V_{DD3} = 3.3 \text{ V} \pm 0.15 \text{ V}, \text{ Vs})$	$s = 0.0 V, T_A = 0 °C to$	+ 70 °C)
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				Va	alue		
Classifica- tion	Parameter	Symbol	V _{DD5} = 5	.0 V ± 5%	VDD5 = 3.3	V ± 0.15 V	Unit
			Min.	Max.	Min.	Max.	
	Delay time	RDYOUT# *		14		15	ns
	Hold time	(External ready mode)	2	_	2	_	ns
Output	Delay time	ERROR#	—	14	—	21	ns
•	Hold time		2	—	2		ns
	Delay time	PDOWN#		14		21	ns
	Hold time	F DOWN#	2	—	2	—	ns
	Setup time	READY#	10	—	10		ns
	Hold time	READT#	2	—	2	—	ns
	Setup time	MEXC#	10	—	10	—	ns
	Hold time		2	—	2	—	ns
	Setup time	D<31:0>	12	—	12	—	ns
	Hold time	D<31.02	2	—	2	—	ns
lonut	Setup time	BREQ#	10	—	10	—	ns
Input	Hold time	DREQ#	2	—	2	—	ns
	Setup time	ВМАСК#1010		ns			
	Hold time	DIVIACR#	2	—	2	—	ns
	Setup time	IRL<3:0>	Asynchronous		Asynchronous		ns
	Hold time	IKL<3.0>	Async	hronous	Asynch	nronous	ns
	Setup time	WKUP#	Asynchronous		Asynchronous		ns
	Hold time	VVKUP#	Async	hronous	Asynch	nronous	ns
	Setup time	RDWR#	12		12		ns
	Hold time		2		2		ns
	Setup time	AS#	12		12		ns
	Hold time	— A3#	2		2		ns
External	Input Setup time	A 61 - 210-	12		12		ns
bus mas- ter input	Hold time	— ASI<3:0>	2	—	2		ns
	Setup time		12		12		ns
	Hold time	— ADR<27:2>	2	—	2		ns
	Setup time	DE0#	12	—	12		ns
	Hold time	— BE2#	2	—	2		ns

(Continued)

(Continued)

		(Vc	$D_3 = 3.3 V \pm$	0.15 V, Vss	$s = 0.0 V, T_A$	$= 0 {}^{\circ}C to +$	(O°C)
o				Va	lue		
Classifica- tion	Parameter	Symbol	$V_{DD5} = 5.$	0 V \pm 5%	$V_{DD5} = 3.3$	$V \pm 0.15 V$	Unit
			Min.	Max.	Min.	Max.	
	Delay time	RAS0# to RAS3#	—	12	—	15	ns
	Hold time	RA30# 10 RA33#	2		2		ns
	Delay time	CAS0# to CAS3#	—	12	—	15	ns
DRAMC	Hold time	CA30# 10 CA33#	2	_	2	_	ns
output	Delay time	DWE0# to DWE3#	—	12		15	ns
	Hold time		2	_	2	_	ns
	Delay time	DOE#	—	12		15	ns
	Hold time	DOE#	2		2		ns
	Setup time		Asynch	ronous	Asynch	ronous	ns
IRC input	Hold time	IRQ15 to IRQ8	Asynch	ronous	Asynch	ronous	ns
into input	"H" level period		$2 \times P + 10$		$2 \times P + 10$		ns
	"L" level period	1	$2 \times P + 10$		$2 \times P + 10$		ns

P:Period (Cycle time)

* : RDYOUT# at the external ready mode is provided for from READY# input.

Notes

- Each parameter is valid within the specified ranges of temperatures and supply voltages unless otherwise noted.
- Each voltage value is based on the GND (Vss = 0.0 V) level. The timing measurement reference point is 1.5 V, the input level is 0.4 to 2.4 V, and the input rise time and fall time are 2 ns or less.
- Do not leave more than one output pins short-circuited for 1 second or more.
- The external output load capacitance is 30 pF.
- The specifications of pins other than those pins designated as asynchronous inputs and than the RDYOUT# pin in external ready mode are determined by the rising edge of the external clock (CLKIN).
- These specifications are subject to change for improvement.
- The reset period requires at least 4 CLKIN cycles. The PLL oscillation stabilization delay time requires at least 4000 clock (CLKIN) pulses. For 40-MHz (25 ns) clock input, for example, the reset signal must therefore be negated 100 μs later.

(4)MB86834-108,-120

Classifica-	Deremeter	C. maked	Va	lue	11
tion	Parameter	Symbol	Min.	Max.	Unit
	CLKIN cycle time	_	25	40	ns
	CLKIN high time	_	8	_	ns
CLK	CLKIN low time	_	8		ns
	CLKIN rising time	—	—	3	ns
	CLKIN falling time	_	—	3	ns
	Delay time	– D<31:0>	—	20	ns
	Hold time	- D<31.0>	2	—	ns
	Delay time	- ADR<27:2>	—	21	ns
	Hold time	- AUK<27.2>	2	—	ns
	Delay time	BE0# to BE3#	—	21	ns
	Hold time		2	—	ns
	Delay time		—	21	ns
	Hold time	- ASI<3.0>	2	—	ns
	Delay time	CS0# to CS5#	—	21	ns
	Hold time		2	—	ns
	Delay time	SAMEPAGE#	—	21	ns
	Hold time	- SAMEFAGE#	2	—	ns
Output	Delay time	RDWR#	—	19	ns
Output	Hold time		2	—	ns
	Delay time	LOCK#	—	19	ns
	Hold time		2	—	ns
	Delay time	AS#	—	19	ns ns
	Hold time	- 43#	2	—	ns
	Delay time	- OVF#		21	ns
	Hold time		2		ns
	Delay time	BGRNT#		19	ns
	Hold time	BORNI#	2		ns
	Delay time	- PBREQ#	_	19	ns
	Hold time		2		ns
	Delay time	BMREQ#		19	ns
	Hold time	DIVIREQ#	2		ns

(Continued)

(V_{DD5} = 3.3 V \pm 0.15 V, V_{DD3} = 2.5 V \pm 0.1 V, V_{SS} = 0.0 V, T_A = 0 °C to ~+ 70 °C)

Classifica-	Baramatar	Symbol	Va	lue	Unit
tion	Parameter	Symbol	Min.	Max.	Unit
	Delay time	RDYOUT#		21	ns
	Hold time	(Internal ready mode)	2	—	ns
	Delay time	RDYOUT# *	_	15	ns
0	Hold time	(External ready mode)	2	_	ns
Output	Delay time			21	ns
	Hold time		2		ns
	Delay time			21	ns
	Hold time	PDOWN#	2	—	ns
	Setup time		Min. $$ 2 $$ 2 $$ 2 $$ 2 $$ 2 $$ 2 10 2 10 2 10 2 10 2 10 2 10 2 10 2 10 2 10 2 10 2 10 2 10 2 10 2 10 2 10 2 12 2 12 2 12 2 12 2 12 2 12 2 12		ns
	Hold time	READT#	2	—	ns
	Setup time	MEXC#	10	—	ns
	Hold time	MEXC#	2	—	ns
	Setup time	D -21:0	— 21 2 — 15 2 2 — 12 — 2 — 12 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 10 — 2 — 10 — 2 — 10 — 2 — Asynchronous Asynchronous Asynchronous Asynchronous 12 — 12 — 12 — 12 — 12 — 12 —	ns	
Input	Hold time	D<31.0>	2	—	ns
	Setup time	PREO#	10	—	ns
	Hold time	DREQ#	2	—	ns
	Setup time	BMACK#	10	—	ns
	Hold time	BWACK#	2	—	ns
	Setup time	IDI -2:05	Asynch	nronous	ns
	Hold time	IKL<3.0>	Asynch	nronous	ns
	Setup time	\\//// ID#	Asynch	nronous	ns
	Hold time		Asynch	nronous	ns
	Setup time		12	_	ns
	Hold time		2	—	ns
	Setup time	$ \begin{array}{ c c c c c c c } & RDYOUT# & & \\ & (Internal ready mode) & 2 & \\ & RDYOUT# * & & \\ & (External ready mode) & 2 & \\ & & \\ & READY mode) & 2 & \\ & & \\ & & \\ & \\ & \\ & \\ & \\ & \\$	—	ns	
	Hold time	A3#	2	—	ns
External	Input setup time	451-220-	12		ns
bus mas- ter input	Hold time	A3I<3.0>	2	—	ns
•	Setup time	ADD -07:05	12	—	ns
	Hold time		2	_	ns
	Setup time	DE 04	READY# 2 — MEXC# 10 — D<31:0> 12 — D<31:0> 2 — BREQ# 10 — BMACK# 10 — RDWR# Asynchronous Asynchronous RDWR# 12 — AS# 12 — ASI<3:0> 12 — ADR<27:2> 12 — BE2# 12 —	<u> </u>	ns
	Hold time	BE2#	2		ns

(Continued)

Classifica-	Parameter	Symbol	Va	lue	Unit
tion	Parameter	Symbol	Min.	Max.	Unit
	Delay time	RAS0# to RAS3#		15	ns
	Hold time	KASU# 10 KASS#	2	_	ns
	Delay time	CAS0# to CAS3#		15	ns
	Hold time	CA30# 10 CA33#	2	_	ns
	Delay time	DWE0# to DWE3#		15	ns
	Hold time		2	_	ns
	Delay time	DOE#		15	ns
	Hold time	DOE#	2	_	ns
	Setup time		Asynch	ronous	ns
IPC input	Hold time	IRQ15 to IRQ8	Asynch	ronous	ns
IRC input	"H" level period		2 × P + 10		ns
-	"L" level period		2 × P + 10		ns

 $(V_{\text{DD5}}=3.3~\text{V}\pm0.15~\text{V},~V_{\text{DD3}}=2.5~\text{V}\pm0.1~\text{V},~V_{\text{SS}}=0.0~\text{V},~T_{\text{A}}=0~^{\circ}\text{C}~to~+70~^{\circ}\text{C})$

P:Period (Cycle time)

* : RDYOUT# at the external ready mode is provided for from READY# input.

Notes

- Each parameter is valid within the specified ranges of temperatures and supply voltages unless otherwise noted.
- Each voltage value is based on the GND (Vss = 0.0 V) level. The timing measurement reference point is 1.5 V, the input level is 0.4 to 2.4 V, and the input rise time and fall time are 2 ns or less.
- Do not leave more than one output pins short-circuited for 1 second or more.
- The external output load capacitance is 30 pF.
- The specifications of pins other than those pins designated as asynchronous inputs and than the RDYOUT# pin in external ready mode are determined by the rising edge of the external clock (CLKIN).
- These specifications are subject to change for improvement.
- The reset period requires at least 4 CLKIN cycles. The PLL oscillation stabilization delay time requires at least 4000 clock (CLKIN) pulses. For 40 MHz (25 ns) clock input, for example, the reset signal must therefore be negated 100 μs later.

(5)MB86835

				lue		
Classifica- tion	Parameter	Symbol	MB8	6835	Unit	
lion			Min.	Max.	1	
	CLKIN cycle time		25	100	ns	
	CLKIN high time	_	8		ns	
CLK	CLKIN low time	_	8		ns	
	CLKIN rising time	_		3	ns	
	CLKIN falling time	_		3	ns	
	Delay time	D 04 0		20	ns	
	Hold time	– D<31:0>	2		ns	
	Delay time	ADD 07:0		21	ns	
	Hold time	– ADR<27:2>	2		ns	
	Delay time			21	ns	
	Hold time	BE0# to BE3#	2		ns	
	Delay time	A QL Q:Q		21	ns	
_	Hold time	– ASI<3:0>	2		ns	
	Delay time	CS0# to CS5#		21	ns	
	Hold time		2		ns	
	Delay time			21	ns	
	Hold time	- SAMEPAGE#	2		ns	
0	Delay time			19	ns	
Output	Hold time		2		ns	
	Delay time			19	ns	
	Hold time	CS0# to CS5# — SAMEPAGE# — SAMEPAGE# 2 RDWR# 2 LOCK# — AS# 2 OVF# —			ns	
	Delay time	A S#		19	ns	
	Hold time	- A0#	2		ns	
	Delay time	O\/E#	_	21	ns	
	Hold time		2	—	ns	
	Delay time	BCDNT#	—	19	ns	
	Hold time	– BGRNT#	2		ns	
	Delay time	- PBREQ#		19	ns	
	Hold time		2		ns	
	Delay time			19	ns	
	Hold time	– BMREQ#	2		ns	

(Continued)

(Continued)

 $(V_{DD3} = 3.3 \text{ V} \pm 0.15 \text{ V}, \text{ V}_{SS} = 0.0 \text{ V}, \text{ T}_{A} = 0 \text{ }^{\circ}\text{C to } + 70 \text{ }^{\circ}\text{C})$

			Va	alue	
Classifica- tion	Parameter	Symbol	MB8	36835	Unit
tion			Min.	Max.	_
	Delay time	RDYOUT#		21	ns
	Hold time	(Internal ready mode)	2		ns
	Delay time	RDYOUT# *		15	ns
0 / /	Hold time	(External ready mode)	2		ns
Output	Delay time	55505#		21	ns
	Hold time	ERROR#	2		ns
	Delay time			21	ns
	Hold time	PDOWN#	2		ns
	Setup time		10		ns
	Hold time		2		ns
	Setup time		10		ns
	Hold time	— MEXC#	2		ns
	Setup time		12		ns
	Hold time	— D<31:0>	2		ns
	Setup time	BREQ# 2	ns		
Input	Hold time	BREQ#	2		ns
	Setup time		10		ns
	Hold time	BMACK#	2		ns
	Setup time		Async	hronous	ns
	Hold time	— IRL<3:0>		hronous	ns
	Setup time		Async	hronous	ns
	Hold time		Async	ns	
	Setup time		12		ns
	Hold time		2		ns
	Setup time		12		ns
	Hold time	AS#	2		ns
External	Input setup time		12		ns
bus mas- ter input	Hold time	— ASI<3:0>	2	<u> </u>	ns
	Setup time		12	_	ns
	Hold time	— ADR<27:2>	2		ns
	Setup time	– – – – – – – – – – – – – – – – – – –	12		ns
	Hold time	— BE2#	2	_	ns
	1		1	1	(Continued)

(Continued)

()		$(V_{DD3} = 3.3 \text{ V} \pm 0.15)$	V, Vss = 0.0 V	$V, T_A = 0 \circ C$	to + 70 °C)		
			Va				
Classifica- tion	Parameter	Symbol	MB8	MB86835			
			Min.	Max.			
	Delay time	RAS0# to RAS3#		15	ns		
	Hold time		2	_	ns		
	Delay time	CAS0# to CAS3#	—	15	ns		
DRAMC	Hold time	- CASU# 10 CASS#	2	—	ns		
output	Delay time	DWE0# to DWE3#	—	15	ns		
	Hold time		2	—	ns		
	Delay time	DOE#	—	15	ns		
	Hold time	DOE#	2	_	ns		
	Setup time		Asynch	ironous	ns		
IRC nput	Hold time	IRQ15 to IRQ8	Asynch	ironous	ns		
	"H" level period		$2 \times P + 10$		ns		
	"L" level period	1	$2 \times P + 10$		ns		

P:Period (Cycle time)

* : RDYOUT# at the external ready mode is provided for from READY# input.

Notes

- Each parameter is valid within the specified ranges of temperatures and supply voltages unless otherwise noted.
- Each voltage value is based on the GND (Vss = 0.0 V) level. The timing measurement reference point is 1.5 V, the input level is 0.4 to 2.4 V, and the input rise time and fall time are 2 ns or less.
- Do not leave more than one output pins short-circuited for 1 second or more.
- The external output load capacitance is 30 pF.
- The specifications of pins other than those pins designated as asynchronous inputs and than the RDYOUT# pin in external ready mode are determined by the rising edge of the external clock (CLKIN).
- These specifications are subject to change for improvement.
- The reset period requires at least 4 CLKIN cycles. The PLL oscillation stabilization delay time requires at least 4000 clock (CLKIN) pulses. For 40 MHz (25 ns) clock input, for example, the reset signal must therefore be negated 100 μs later.
- An AC characteristic of pins and internal maximum operation frequency is separately defined.
- The maximum operation frequency of an external bus is 40MHz though the maximum internal operation frequency are 80 MHz or 100 MHz (CLKIN Min.=25ns).Therefore,when an external bus is used with 40MHz, an internal frequency are 84 MHz and 100 MHz.
- Relation between external bus clock and internal clock

CLKIN	MB86835(84MHz)									
CLAIN	× 1	× 2	× 3	× 4	× 5					
20 MHz	20 MHz	40 MHz	60 MHz	80 MHz	N/A					
33.3 MHz	33.3 MHz	66.6 MHz	N/A	N/A	N/A					
40 MHz	40 MHz	80 MHz	N/A	N/A	N/A					

(6)MB86836-90,-108(Preliminary)

Classifica-	Parameter	Cymh el	Va	lue	Unit
tion	Parameter	Symbol	Min.	Max.	
	CLKIN cycle time		25	40	ns
	CLKIN high time		8		ns
CLK	CLKIN low time		8		ns
	CLKIN rising time	_	_	3	ns
	CLKIN falling time		_	3	ns
	Delay time	– D<31:0>	_	20	ns
	Hold time	- D<31.0>	2		ns
	Delay time	- ADR<27:2>	_	21	ns
	Hold time	ADR<27.2>	2		ns
	Delay time	BE0# to BE3#		21	ns
	Hold time		2		ns
	Delay time	- ASI<3:0>		21	ns
	Hold time	- ASI<3.0>	2		ns
-	Delay time	- CS0# to CS5#	_	21	ns
	Hold time		2		ns
	Delay time	SAMEPAGE#	_	21	ns
	Hold time	- SAIWEFAGE#	2		ns
Output	Delay time	- RDWR#	_	19	ns
Output	Hold time		2		ns
	Delay time	LOCK#	_	19	ns
	Hold time		2	—	ns
	Delay time	AS#	_	19	ns
	Hold time	- 43#	2		ns
	Delay time	- OVF#		21	ns
	Hold time	011#	2		ns
	Delay time	BGRNT#		19	ns
	Hold time		2		ns
	Delay time	- PBREQ#		19	ns
	Hold time		2		ns
-	Delay time	- BMREQ#		19	ns
	Hold time	DivirteQ#	2		ns

(Continued)

(V_{DD5} = 3.3 V \pm 0.15 V, V_{DD3} = 2.5 V \pm 0.1 V, V_{SS} = 0.0 V, T_A = 0 °C to ~+ 70 °C)

Classifica-	Description	Sumaly al	Va	lue		
tion	Parameter	Symbol	Min.	Max.	Unit	
	Delay time	RDYOUT#		21	ns	
	Hold time	(Internal ready mode)	2		ns	
	Delay time	RDYOUT# *		15	ns	
	Hold time	(External ready mode)	2	_	ns	
Output	Delay time		_	21	ns	
	Hold time	ERROR#	2	_	ns	
	Delay time			21	ns	
	Hold time	PDOWN#	2	_	ns	
	Setup time		10		ns	
	Hold time		2		ns	
	Setup time	MEX0#	10	_	ns	
	Hold time	— MEXC#	2		ns	
	Setup time	D -21:0	12		ns	
	Hold time	— D<31:0>	2	—	ns	
Input -	Setup time	BREQ#	10	—	ns	
	Hold time	BREQ#	2	—	ns	
	Setup time	BMACK#	10	—	ns	
	Hold time	BinACK#	2	—	ns	
	Setup time	IRL<3:0>	Asynch	ns		
	Hold time	IKL<3.0>	Asynch	ns		
	Setup time	WKUP#	Asynch	nronous	ns	
	Hold time		Asynch	nronous	ns	
	Setup time	RDWR#	12	_	ns	
	Hold time		2	—	ns	
	Setup time	AS#	12	—	ns	
	Hold time	A3#	2	—	ns	
External bus mas-	Input setup time	ASI<3:0>	12		ns	
ter input	Hold time	A3I<3.0>	2	—	ns	
·	Setup time	ADD -07:05	12	—	ns	
	Hold time	— ADR<27:2>	2	_	ns	
ç	Setup time	DE 04	12	<u> </u>	ns	
	Hold time	— BE2#	2	_	ns	

(Continued)

Classifica-	Parameter	Symbol	Va	lue	Unit
tion	Farameter	Symbol	Min.	Max.	Unit
	Delay time			15	ns
	Hold time	RAS0# to RAS3#	2	_	ns
	Delay time	CAS0# to CAS3#		15	ns
DRAM-	Hold time	CAS0# 10 CAS5#	2	_	ns
Coutput	Delay time	DWE0# to DWE3#		15	ns
	Hold time		2	_	ns
	Delay time	DOE#		15	ns
	Hold time	DOE#	2	_	ns
	Setup time		Asynch	ronous	ns
IPC input	Hold time	IRQ15 to IRQ8	Asynch	ronous	ns
IRC input	"H" level period		2 × P + 10		ns
	"L" level period		$2 \times P + 10$		ns

 $(V_{DD5} = 3.3 \text{ V} \pm 0.15 \text{ V}, V_{DD3} = 2.5 \text{ V} \pm 0.1 \text{ V}, V_{SS} = 0.0 \text{ V}, T_A = 0 \text{ }^{\circ}\text{C} \text{ to } + 70 \text{ }^{\circ}\text{C})$

P:Period (Cycle time)

* : RDYOUT# at the external ready mode is provided for from READY# input.

Notes

- Each parameter is valid within the specified ranges of temperatures and supply voltages unless otherwise noted.
- Each voltage value is based on the GND (Vss = 0.0 V) level. The timing measurement reference point is 1.5 V, the input level is 0.4 to 2.4 V, and the input rise time and fall time are 2 ns or less.
- Do not leave more than one output pins short-circuited for 1 second or more.
- The external output load capacitance is 30 pF.
- The specifications of pins other than those pins designated as asynchronous inputs and than the RDYOUT# pin in external ready mode are determined by the rising edge of the external clock (CLKIN).
- These specifications are subject to change for improvement.
- The reset period requires at least 4 CLKIN cycles. The PLL oscillation stabilization delay time requires at least 4000 clock (CLKIN) pulses. For 40 MHz (25 ns) clock input, for example, the reset signal must therefore be negated 100 μs later.
- An AC characteristic of pins and internal maximum operation frequency is separately defined.
- The maximum operation frequency of an external bus is 40MHz though the maximum internal operation frequency are 90 MHz or 100 MHz (CLKIN Min.=25ns).Therefore,when an external bus is used with 40MHz, an internal frequency is 80 MHz

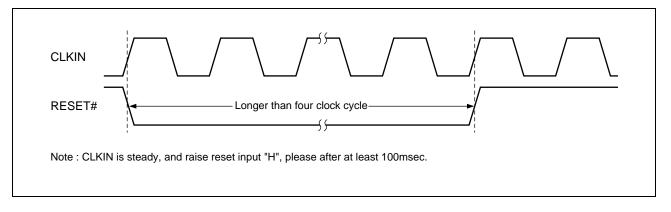
CLKIN		MB8683	6(90MHz)			MB86836(108MHz)*							
CLKIN	× 1	× 2	× 3	× 4	× 5	× 1	× 2	× 3	× 4	× 5			
27 MHz	27 MHz	54 MHz	81 MHz	N/A	N/A	27 MHz	54 MHz	81 MHz	108 MHz	N/A			
33.3 MHz	33.3 MHz	66.6 MHz	N/A	N/A	N/A	33.3 MHz	66.6 MHz	100MHz	N/A	N/A			
36 MHz	36MHz	72 MHz	N/A	N/A	N/A	36MHz	72 MHz	108MHz	N/A	N/A			
40 MHz	40 MHz	80 MHz	N/A	N/A	N/A	40 MHz	80 MHz	N/A	N/A	N/A			

• Relation between external bus clock and internal clock

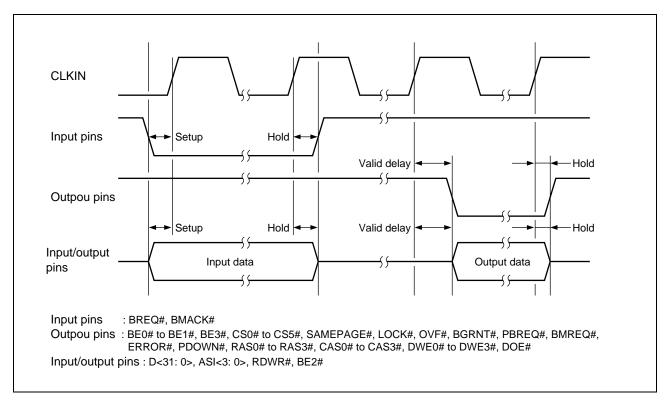
*: MB86836 108MHz version is under developement.

TIMING DIAGRAM

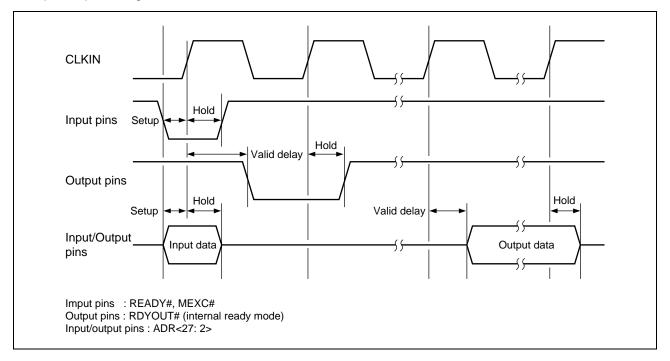
· Reset timing



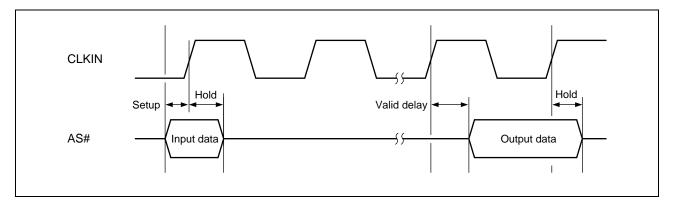
• Input/output timing 1



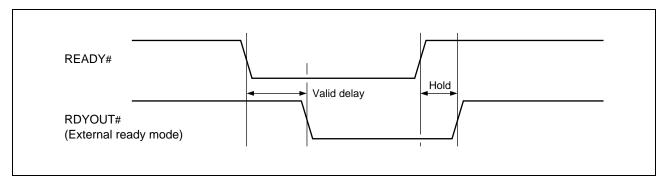
• Input/output timing 2



• Input/output timing 3



• Input/output timing 4



■ ARCHITECTURE

The MB86830 series is a line of 32-bit RISC processors running at an operating frequency of 100 MHz, providing high performance of 121 VAX-MIPS. As products belong to the Fujitsu SPARClite family, the MB86830 series is based on the SPARC architecture and are thus upward code-compatible with the conventional products in the SPARClite family. The MB86830 series was developed in particular for embedded applications, providing high performance and high level of integration when used as embedded controllers.

The MB86830 series has an efficient set of instructions and is hardwired so that most of them can be executed in one cycle. The IU (integer unit) features five pipelined execution stages designed for processing data interlocks, providing a branch handler optimized for for efficient transition of control and a bus interface for processing one-cycle bus access for on-chip memory.

The internal register file consisting of a stack of eight windows, made up of 136 registers in total, speeds up interrupt response and context switching. The register file minimizes memory access during procedure linkage and facilitates parameter passing and variable assignment.

The MB86830 series contains instruction and data caches to isolate processor operation from external memory. These caches are designed for highest flexibility so that it can lock each entry to improve the performance of the entire system.

The independent instruction and internal data buses serve as high-bandwidth interfaces between the IU (integer unit) and the on-chip caches. These buses support single-cycle instruction execution and single-cycle data transfer between the IU and caches in parallel.

The MB86830 series incorporates an integer multiplier and auxiliary hardware for division. The MB86830 series can therefore execute 32-bit integer multiplication in five cycles, 16-bit integer multiplication in three cycles, 8-bit integer multiplication in two cycles, and integer multiplication by 0 in one cycle.

1. Main Features

(1)High-speed execution of instructions

Most of the instructions in most programs are simple, designing the programs so as to execute such simple instructions as fast as possible dramatically improves the program execution time.

(2)High-capacity register set

The register set reduces the number of required accesses to data memory. Registers are organized into a stack of groups called register windows, allowing themselves to be used efficiently for high-priority tasks such as interrupt services and operating system working registers. A stack of (overlapping) register windows also contributes to simplifying parameter passing during procedure linkage, thereby reducing the code size of most programs.

(3)On-chip caches

The MB86830 series incorporates data and instruction caches so that the processor can work independently of the slower memory subsystem. These caches are implemented in two-way set-associative configuration on the MB86831/832; they are directly mapped on the MB86833.

(4)Locking entries in caches

The MB86830 series can lock both of data and instruction entries in their respective caches, ensuring high performance in processing important or frequently called routines. Each cache offers maximum flexibility so that entries can be locked in all or selective part of the cache.

(5)Bus interface

The MB86830 series supports programmable chip selection, a wait state generator, and fast page mode DRAM, minimizing the necessity of connecting external circuits.

(6)On-chip DRAM controller

The on-chip DRAM controller supports fast page mode and EDO DRAMs. It also controls self-refreshing of DRAM in sleep mode (low power consumption mode).

(7)On-chip interrupt controller

The on-chip interrupt controller accepts interrupt inputs through eight channels, allowing a trigger mode to be set independently for each of the channels. The interrupt request accepted according to the trigger mode is encoded and output to the processor.

(8) Multiplier circuit

The MB86830 series incorporates a multiplier circuit which can be selectively set to an operating clock frequency of x1, x2, x3, x4, or x5 of the external clock frequency, allowing the processor to run at high speed.

(9) Instruction set

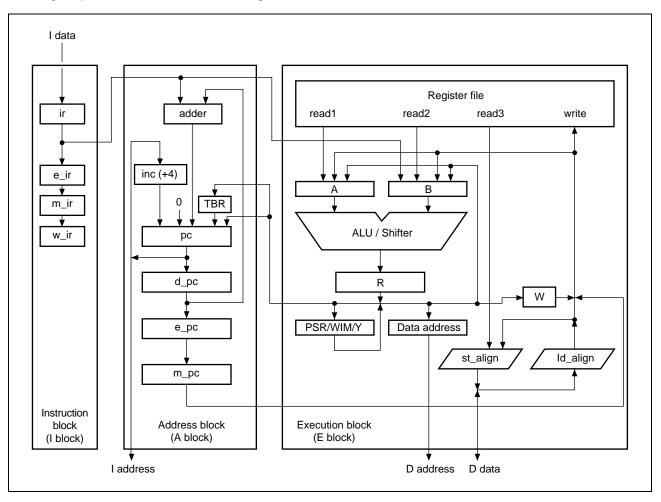
The MB86830 series supports high-speed integer multiply instructions which are executed in five, three, and two cycles respectively for 32-, 16-, and 8-bit multiplications. The integer divide step instruction is near 10 times faster in divide time than the previous SPARC implementation. The scan instruction supports the function for detecting 1 or 0 at the MSB in a word in a single cycle.

2. CPU

The CPU core of the MB86830 series is a high-performance version implemented by full custom design of the SPARC architecture. The CPU core contains a compact circuitry for integrating peripheral circuits, designed to be customizable to a variety of applications. The CPU core consists of three function units: instruction, address, and execution blocks (see "Integer operation unit internal block diagram").

The role of five execution stages for instruction pipelining is to decode all instructions and generate control signals for other blocks. The five pipelined stages are the fetch (F), decode (D), execute (E), memory (M), and write back (W) stages. The instruction memory returns an instruction addressed at stage (F), the register file returns an operand addressed at stage (D), the ALU perform calculation to obtain the result at stage(E), the external memory is addressed at stage (M), and the register file is written back at stage (W).

• Integer operation unit internal block diagram



3. Address Space

The MB86830 series has a wide addressable range in which user and supervisor spaces can be defined independently. Of 30 lines of addresses, eight lines of address space identifiers (ASI) are used to distinguish between protected and unprotected spaces. Tow of 256 different ASI values are used to define the user data and user instruction spaces; the rest are used to define the supervisor space.

When a reset, synchronous trap, or asynchronous trap occurs, the processor enters the supervisor mode. In the supervisor mode, the processor executes instructions in the supervisor space and transfers data. The processor can access other ASI values even when staying in the supervisor mode. The processor can use the remaining ASI values, excluding the reserved values, to allocate other spaces as application definable spaces.

By distinguishing between the user and supervisor spaces, hardware can prevent inadvertent or unauthorized access to system resources. When a real-time operating system (RTOS) is developed, for example, individual spaces provide the mechanism for separating the RTOS space efficiently from the user space.

4. Registers

The register set of the MB86830 series is made up of the registers to be used for general-purpose functions and those to be used for control and status report purpose. The MB86830 series has 136 general-purpose registers divided into eight global registers and a stack of eight register blocks (register windows). Each register window incorporates 24 registers, of which eight registers are local to that window, eight "out" registers are overlapping the next register window. (See "General register composition".)

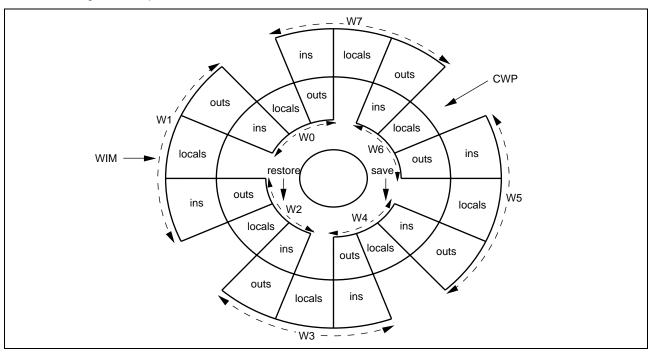
This register configuration allows a parameter to be passed to a subroutine. The next register window is made

available b writing the parameter to be passed to the "out" register and using a procedure call to decrement the window pointer by one. The passed parameter remains in the "in" registers in the current register window and can be used by that subroutine.

Register windows improve the performance of embedded applications. This is because these windows serve as the local variable caches for storing interrupt, subroutine, context, or operating system variables without increasing overhead. In addition, the code size of programs can be reduced by using an efficient method of executing procedure linkage without optimizing the code using an inlining compiler.

The register file consists of 4-port registers: 3-port read and 1-port write registers. Even the store instruction can therefore be executed in one cycle, which requires three operands to be read from the register file.

The control and status registers are divided into those defined in the SPARC architecture and those mapped into the alternate address space for controlling the functions of peripheral devices.



• General register composition

5. Instruction Set

The MB86830 series is upward code-compatible with other SPARC processors. The MB86830 series now supports additional instructions to improve performance, which were previously not directly supported. In addition to a set of already supported SPARC instructions, the MB86830 series has been provided with the integer multiply and integer divide step instructions as well as the scan instruction for detecting "1" or "0" at the MSB. For the list of supported instructions, see the instruction set below.

• Instruction set

LOGICAL	ARITHMETIC/SHIFT	DATA MOVEMENT
CONDITION CODES UNCHANGED AND OR XOR AND NOT OR NOT XNOR CONDITION CODES SET AND OR XOR AND NOT OR NOT XNOR CONTROL TRANSFER CONDITIONAL BRANCH CONDITIONAL BRANCH CONDITIONAL BRANCH CONDITIONAL TRAP CALL RETURN SAVE RESTORE JUMP AND LINK	CONDITION CODES UNCHANGED ADD SUBTRACT MULTIPLY (SIGNED/UNSIGNED) SCAN SETHI SHIFT LEFT LOGICAL SHIFT RIGHT LOGICAL SHIFT RIGHT ARITHMETIC CONDITION CODES SET ADD SUBTRACT MULTIPLY (SIGNED/UNSIGNED) MULTIPLY STEP DIVIDE STEP EXTENDED AND CONDITION CODES UNCHANGED ADD SUBTRACT EXTENDED AND CONDITION CODES SET ADD SUBTRACT TAGGED AND CONDITION CODES SET (WITH AND WITHOUT TRAP ON OVERFLOW) ADD SUBTRACT	TO USER/SUPERVISOR SPACE SIGNED LOAD BYTE LOAD HALF-WORD LOAD WORD LOAD DOUBLE WORD STORE BYTE STORE HALF-WORD STORE MORD STORE DOUBLE WORD TO USER SPACE UNSIGNED LOAD BYTE LOAD HALF-WORD TO ALTERNATE SPACE SIGNED LOAD WORD LOAD DOUBLE WORD STORE BYTE STORE HALF-WORD STORE BYTE STORE HALF-WORD STORE WORD STORE DOUBLE WORD STORE DOUBLE WORD STORE DOUBLE WORD DALTERNATE SPACE UNSIGNED LOAD BYTE LOAD HALF-WORD STORE DOUBLE WORD STORE DOUBLE WORD STORE DOUBLE WORD DALTERNATE SPACE UNSIGNED LOAD BYTE LOAD HALF-WORD
READ/WRITE CO	DNTROL REGISTER	LOAD/STORE UNSIGNED BYTE
READ PSRREAD WWRITE PSRWRITE VREAD TBRREAD YWRITE TBRWRITE Y	VIM WRASR	ATOMIC OPERATION IN ALTERNATE SPACE SWAP WORD LOAD/STORE UNSIGEND BYTE

6. Interrupts

One of the key criteria to determine whether a processor is suitable for embedded applications is whether the processor can completely service interrupts within the minimum interrupt processing time. The processors implemented as the MB86830 series guarantee not only short average wait time but also short maximum wait time. The interrupt response time is the sum of the time for the processor to complete the current task after recognizing an interrupt and the time for the processor to start executing the interrupt service routine. The MB86830 series offers a variety of functions to minimize the both factors.

To minimize the time to complete the current task, the MB86830 series is designed so that the task can be interrupted easily or it can be completed in a minimum of cycles. For this purpose, the MB86830 series implements the cache system that updates only one word at a time using a prefetch buffer when a cache miss occurs, interruptible integer division using a divide step instruction, high-speed multiplication using a multiplier, and a 4-word write buffer for processing a pending bus transaction.

To minimize the time required for starting executing the interrupt service routine, the processor switches the register window to a new one upon detection of an interrupt. This function allows the service routine to be executed without saving the current register in advance. The user can also lock the service routine in the cache, allowing faster processing with the routine. At this time, the on-chip data cache can be used as a high-speed local stack to minimize the delay in accessing the routine variable in the service routine.

The MB86830 series has a maximum of 15 interrupt levels to directly support 15 interrupt sources. The highest interrupt level is nonmaskable.

7. Caches

The MB86830 series incorporates independent data and instruction caches, allowing a high-performance system to be constructed without the need for high-speed external memory or relevant control logics. The caches are mapped onto physical addresses.

The instruction cache consists of: 64 units/2 banks on the MB86831/835, 128 units/2 banks on the MB86832/836, 256 units/2 banks on a 32-byte line on the MB86834, and 64 units/1 bank on a 16-byte line on the MB86833. The data cache consists of: 64 units/2 banks on the MB86831/835, 64 units/1 bank on a 16-byte line on the MB86833, 128 units/2 banks on the MB86832/836, and 256 units/2 banks on a 32-byte line on the MB86832/836, and 256 units/2 banks on a 32-byte line on the MB86834. (See "The composition of the data cache" and "The composition of the instruction cash.") Each line is divided into 4-byte subblocks. When a cache miss occurs, the cache is updated in one word (4 bytes) or four words (16 bytes), selectively. Updating the cache in one word eliminates the wait time for an interrupt generated for replacing a long cache line;

updating the cache in four words can result improvement in cache hit rate.

Updating the cache in four words uses the burst mode. The instruction prefetch buffer fetches the next instruction in advance, assuming that it corresponds to the next instruction cache miss.

The caches can be used in the normal mode or in either of two lock modes. In the normal mode, the cache in twoway set-associative configuration replaces one of two corresponding entries using the LRU (Least Recently Used) algorithm. As an alternate method, the entire cache or only the selected entry can be locked depending on the lock mode in use. The lock mode can lock a time-critical routine in the cache. The global cache lock mode locks the entries in the entire instruction or data cache.

The two control bits in the cache control register enable or disable the lock in the instruction and data caches. Once an entire cache is locked, any valid entry in the cache cannot be replaced. To ensure optimum performance, however, an invalid entry is updated when it is accessed. This update is performed automatically without generating time penalty. The instruction or data entry selected by local cache locking can be locked automatically in the corresponding cache. This mechanism can ensure the fastest response from a certain important interrupt routine by locking the code of the routine in the cache.

Also, of those routines which can be removed from the cache, frequently used ones should be given priority in performance in some cases. In such cases, the entries can be locked.

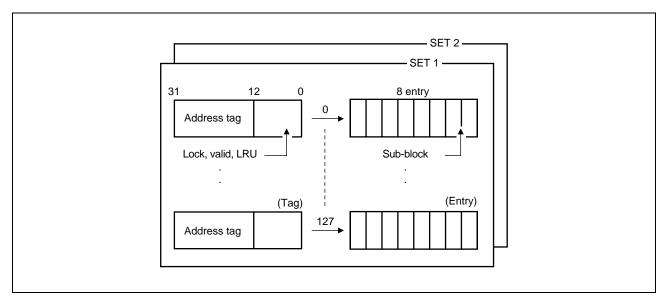
The local cache lock mode can lock individual entries or lock entries automatically by hardware. To lock each entry, the lock bit in the corresponding cache tag line is set by software. For automatic cache locking, the lock function is enabled or disabled depending on the bit in the corresponding cache control register. The enable/disable bit is set at the beginning of the routine for which the entry is to be locked. The location of cache access generated with the bit enabling the lock function is locked in the cache. Automatic cache locking does not involve overhead other than the initial setting cycle.

When a cache entry is unlocked, the data cache assign the cache entry only at load time based on the writethrough update policy. The write operation is buffered and the processor can continue execution while data is being written back to memory. In contrast, the data written to the locked data cache location is not written to main memory.

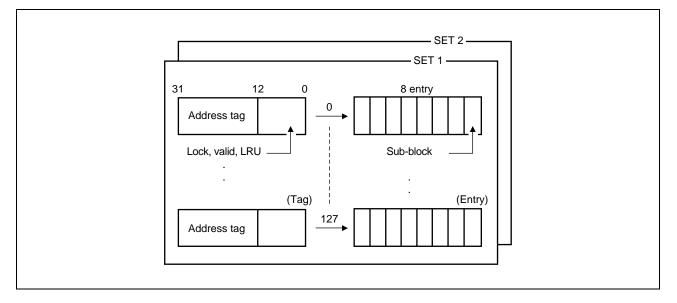
The above method reduces external bus access and allows part of the data cache to be used as on-chip RAM which is not mapped into external memory.

The data and instruction caches are designed to be accessed through the independent data and instruction buses to load/write data from/to the cache at a maximum speed of 1 CPI (Clock/Instruction).

• The composition of the data cache (For MB86832).



• The composition of the instruction cash (For MB86832).



8. Bus Interface

The bus interface unit (BIU) is designed to simplify the interface between the MB86830 series and other parts of the system. The non-multiplexed address bus and data bus allow a high-speed system to be constructed easily. Also, the internal circuitry allows such a system to be constructed with a minimum of external hardware. The bus interface supports programmable wait state generation, chip select output by address decoding, same-page detection for supporting page mode DRAM, booting from 8/16/32-bit memory, and a automatic reload timer for refreshing DRAM. In addition, the burst mode can be used to perform cache line fill operation at high speed.

9. DRAM Controller

With the DRAM controller controlling DRAM, the MB86830 series can write/read data to/from DRAM. The DRAM controller can control up to four banks on the MB86831/832/834 or only one bank on the MB86833/835. The fast page mode, DRAM mode, or EDO DRAM mode can be selected depending on the register setting. The DRAM

controller also controls the RAS and CAS to place DRAM in the self-refresh mode when the processor enters the sleep mode (low power consumption mode).

The MB86836 has no DRAM controller.

10. Interrupt Controller (IRC)

The interrupt controller (IRC) accepts interrupts inputs through eight channels, depending on the trigger mode and mask bit set for each of the channels. When accepting an interrupt, the interrupt controller encodes it according to the interrupt priority level and outputs the interrupt level to the processor. The interrupt level remains held unless it is cleared by the processor. The processor is not therefore informed of the next interrupt.

11. Multiplier Circuit

The CLKSEL0, CLKSEL1, and CLKSEL2 pins can be used to select the multiplier circuit to be used. The \times 1, \times 2, \times 3, \times 4, or \times 5 multiplier circuits are supported, which allow the processor to run faster.

12. IU (Integer Unit) Dedicated Registers (Not Memory Mapped)

(1)Processor Status Register (PSR)

$bit \rightarrow$	31 23	3 27	24	23			20	19	12	11	1	8	7	6	5	4 3	2	2 0
	0000н	0. 1111	1111 н		ic	с		Reserved		PIL		n	PS	ET	Reserved	1	CWP	
	00004		I IH	n	z	v	С		eserveu		I IL		3	13		Reserved		CWI

bit 23 to bit 20 :Integer condition code [icc] (n:Negative = 1, z:Zero = 1, v:Overflow = 1, c:Carry = 1)

bit 19 to bit 12 :Reserved["0"Write, Don't care for read]

bit 11 to bit 8	:Processor Interrupt Level [PIL] (Value = 1 to 15, RST = X)
bit 7	:Supervisor Mode [S] (Supervisor = 1, User = 0, RST = 1)
bit 6	:Prior S Mode [PS]
bit 5	:Enable Trap [ET] (Enable = 1, Disable = 0, RST = 0)
bit 4 to bit 3	:Reserved ["0"Write, Don't care for read]
bit 2 to bit 0	:Current Window Point [CWP] (Value = 0 to 7, RST = X)

X:Don't care

(2)Window Invalid Mask Register (WIM)

$\text{bit} \rightarrow$	31 8	7	6	5	4	3	2	1	0
	Reserved	w7	w6	w5	w4	w3	w2	w1	w0

bit 31 to bit 8 :Reserved ["0"Write, Don't care for read]

bit 7 to bit 0 :Window mask [w7 to w0] (Invalid = 1, Valid = 0, RST = X)

X:Don't care

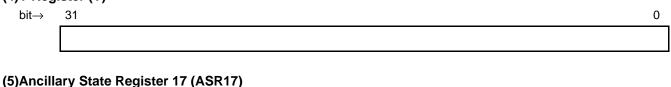
(3)Trap Base Register (TBR)

$\text{bit} \rightarrow$	31 12	11	4	3	0
	ТВА	tt		0000)

bit 31 to bit 12 :Trap base address [TBA] (RST = X) bit 11 to bit 4 :Trap type [tt] (RST = X)

X:Don't care

(4)Y Register (Y)



0

0

$bit \rightarrow$ 31 1 SVT Reserved

bit 31 to bit 1 :Reserved ["0"Write, Don't care for read]

:Single Vector Trapping [SVT] (Enable = 1, Disable = 0, RST = 0) bit 0

13. IU (Integer Unit) General-Purpose Registers (Not Memory Mapped)

The IU (integer unit) contains 136 32-bit general-purpose registers for holding arguments for operations and their results. Of these registers, only 32 registers can be accessed through blocks called register windows. The integer unit has eight register windows. The register window to be used is determined by the CWP bits (bits 2 to 0) in the Processor Status Register (PSR). Each register window consists of eight global registers available commonly to all register windows and 24 registers (in-register \times 8, local register \times 8, out-register \times 8). The in-registers and out-registers are used commonly between adjacent register windows.

(1)Zero Register (r0)

$\text{bit} \rightarrow$	31		0
		0	
bit 31 to b	it 0 :0		
(2)Genera	al register (r1 to r31)		

 $bit \rightarrow$ 31

Don't care at reset.

14. Bit map of register with built-in CPU core

(1)Cache/BIU Control Register (CBIR)				SI=	0x0	1, A	ddr	ess:	= 0x	000	0000)О н
$\text{bit} \rightarrow$	31 1	10	9	8	7	6	5	4	3	2	1	0
	Reserved											

bit 31 to bit 10	:Reserved ["0"Write, Don't care for read]
bit 9 to bit 8	:Non-cacheable Wait-state [Don't care for read]
bit 7	:Cacheability Enable [Don't care for read] (Enable = 1, Disable = 0, RST = 0)
bit 6	:Reserved ["0"Write, Don't care for read]
bit 5	:Write Buffer Enable (Enable = 1, Disable = 0, RST = 0)
bit 4	:Prefetch Buffer Enable (Enable = 1, Disable = 0, $RST = 0$)
bit 3	:Data Cache Lock (Lock = 1, Unlock = 0, RST = 0)
bit 2	:Data Cache Enable (Enable = 1, Disable = 0, $RST = 0$)
bit 1	:Instruction Cache Lock (Lock = 1, Unlock = 0 , RST = 0)
bit 0	:Instruction Cache Enable (Enable = 1, Disable = 0, $RST = 0$)

Lock Contr bit→ 31	ol Register (LCR)	ASI=	• UXU1,	Auu	ress	s= 0>	x00(2	0 00 0 1	004 0
	Reserved						_		
31 to bit 2	:Reserved ["0"Write, Don't care for read] :Data Cache Entry Auto Lock (Enable = 1, Disable = 0, :Instruction Cache Entry Auto Lock (Enable = 1, Disable								
_ock Contr bit→ 31	ol Save Register (LCSR)	ASI =	0x01, /	Addr	ess	= 0 x	2)000	80(
	Reserved								
31 to bit 2 1 0	:Reserved ["0"Write, Don't care for read] :Previous Data Cache Auto Lock (Off = 0, On = 1, RST = :Previous Instruction Cache Auto Lock (Off = 0, On = 1,	,							
Restore Lo bit→ 31	ck Control Register (RLCR)	ASI = ()x01, A	ddre	ess =	= 0x	000)000	0 10 0
	Reserved								
	:Reserved ["0"Write, Don't care for read] :Restore Lock Control Register (Restore = 1, Ignore = 0,	RST = 0)						
0 Bus Contro	:Reserved ["0"Write, Don't care for read] :Restore Lock Control Register (Restore = 1, Ignore = 0, ol Register (BCR)) 0x01, /	Addr	ess	= 0x	2)000	
) Bus Contro	:Restore Lock Control Register (Restore = 1, Ignore = 0,		,	٩ddr	ess	= 0 x			
Bus Contro bit \rightarrow 31	:Restore Lock Control Register (Restore = 1, Ignore = 0,	ASI =	,	Addr	ess	= 0 x			
0 Bus Contro bit→ 31 31 to bit 2 1 0 System Su	:Restore Lock Control Register (Restore = 1, Ignore = 0, DI Register (BCR) Reserved :Reserved ["0"Write, Don't care for read] :Data Burst Enable (Enable = 1, Disable = 0, RST = 0)	ASI = = 0) ASI =	0x01, /	Addr	ess	= 0 x	2	1 0000	0 80
bit \rightarrow 31 31 to bit 2 1 0	:Restore Lock Control Register (Restore = 1, Ignore = 0, Pl Register (BCR) Reserved :Reserved ["0"Write, Don't care for read] :Data Burst Enable (Enable = 1, Disable = 0, RST = 0) :Instruction Burst Enable (Enable = 1, Disable = 0, RST = 0)	ASI = = = 0)	0x01, /				2	1	0

*:CS0 is always enable.

′)Same bit→	-	30		22	22									٬ 00000	
DII→	31		01 70 14-	-	22		A -1-		Maal					1	
			ASI<7:0>Mas	SK			Add	dress<31:10)>IVIask						
t 31 t 30 to t 22 to t 0		3 :ASI :Ado	<7:0>Mask	(Care = >Mask	= 0, Do (Care	are for read] on't Care = 1, F = 0, Don't Car re for read]									
Don't d	care														
-		-	Specifier R	-	•	SR) A	SI = 0x0	1, Addres	s = 0x	0000	012	24н t	o 0x	00000 [,]	13
$bit \rightarrow$	31	30		23	22									1	-
			ASI<7:0>					Address<31	:10>						
Don't d	care			ŗ	dress∙	<14: 10>=0,AS			s = 0x	0000	0014	Юн t	o 0x	00000 [,]	15
Don't d	care ess N	lask R 30	egister (AM	IR) 23	dress 22	·	SI = 0x0	1, Addres			0014	Юн t	o 0x	00000 ^ 1	
Don't d)Addre	care ess N	lask R 30		IR) 23		·	SI = 0x0				0014	Юн t	o 0x		
Don't c)Addre bit→ t 31 t 30 to t 22 to t 0 Don't c	bit 23	lask R 30 :Res 3 :ASI :Add :Res	egister (AM ASI<7:0>Mas erved ["0"W <7:0>Mask ress<31:10	IR) 23 k /rite, Dc (CS0:R >Mask /rite, Dc	22 on't ca ST = (CS0: on't ca	A are for read] 0, CS1 to CS5 RST = <31:15: are for read]	SI = 0x0 Add RST = 3 > = 0, <1	1 1, Addres dress<31:10	⊳Mask <1f, CS	61 to	CS	5:RS	ST = 1	1 X)	Ţ
Don't c bit→ t 31 t 30 to t 22 to t 0 Don't c 0)Wait	bit 23	Iask R 30 :Res :ASI :Add :Res	egister (AM ASI<7:0>Mas erved ["0"W <7:0>Mask ress<31:10 erved ["0"W ifier Regis	IR) 23 sk /rite, Dc (CS0:R >Mask /rite, Dc	22 on't ca ST = ((CS0: on't ca	A are for read] 0, CS1 to CS5 RST = <31:15: are for read] A	SI = 0x0 Add RST = 2 > = 0, <1 SI = 0x0	1, Addres dress<31:10 (X) 4:10> = 0 1, Addres	>Mask <1f, CS	61 to	CS:	5:RS	ST = 1	1 X)	16
Don't c)Addre bit→ t 31 t 30 to t 22 to t 0 :Don't c	bit 23 bit 23 bit 1 care	Iask R 30 :Res :ASI :Add :Res	egister (AM ASI<7:0>Mas erved ["0"W <7:0>Mask ress<31:10 erved ["0"W ifier Regis	IR) 23 k /rite, Dc (CS0:R >Mask /rite, Dc	22 on't ca ST = ((CS0: on't ca	A are for read] 0, CS1 to CS5 RST = <31:15: are for read] A	SI = 0x0 Add RST = 3 > = 0, <1	1, Addres dress<31:10 (X) 4:10> = 0 1, Addres	>Mask <1f, CS	61 to	CS:	5:RS 50н t	ST = 1	1 X)	

(11)Bus	Width/Cach	eable R	egister	(BWCF	र)				ASI	= 03	c0 1,	Ad	dre	ess =	= 0x0	0000	016Cн
$\text{bit} \rightarrow$	31 24	23 22	21 20	19 18	17 16	15 14	13 12	11 10	9	8	7	6	5	4	3	2 1	0
	Reserved	CS5	CS4	CS3	CS2	CS1	CS0	CS5	С	S4	CS	S3	С	S2	CS	1	
bit 22,bit	21,bit 19,bit 20,bit 18,bit bit 10,bit 9 to it 2	16,bit 14	4,bit 12	6,bit 5	to bit 4,	:lr :C :B	eserveo nternal/E acheab us Widt eserveo	External le (0 = c h Contr	Cao cach ol bi	chea ieab it	able le, 1	(0 = l = n	ion	tern cach	ial, 1 neabl		ernal)
(12)DRA	M Refresh T	imer Re	egister	(REFT	MR)	A	SI = 0x0	1, Add	ress	s = 0	x00	000	174	4н			
$\text{bit} \rightarrow$	31 30					16	15										0
			Rese	erved						T	imer	Valu	Je				
bit 15 to l	bit 16 :Rese	r Value	"Write, (RST =	Don't ca 0xffff)	are for r	ead]	15		ASI	l = 0	x01	, Ad	dre	ess :	= 0x(0000	0178 н 0
			Rese	erved		_	-		Ti	imer	Pre-	load	Va	lue			_
bit 15 to l	bit 16 :Rese bit 0 :Time	r Pre-loa	"Ŵrite, ad Valu	Don't ca e (RST	are for r = 0xffff)	ead]											
(14)Anci bit→	Ilary Version 31	n Regis	ter (VEI	R2)[Rea	ad only	-	15		AS	I = 0	XU1	, Ad	are	ess	= UX(002	0000 н 0
			Reserv	ed		10	10				Ver	sion					
bit 15 to l (MB8683	Lbit 16 :Rese bit 0 :Vers 1:Value = 0, 5:Value = 4, I	ion MB868	on't car 32:Valu	e for rea e = 1, N	-	3:Value	= 2, ME	386834:	Valu	ie =							
	p Mode Reg	ister (S	LPMD)[Write o	only]				ASI	 = 0	x01	, Ad	dre	ess	= 0x(0002	0004 н
bit→	31					Rese	erved										1 0
						1000											
bit 31 to I	bit 1 :Rese	erved	(On 1			(\mathbf{x})											

bit 0 :Sleep Mode (On = 1, Off = 0, RST = 0)

15. Bit map of register for cash access	
(1)Instruction Tag Lock Bit (ICLOCK) [Wite only]	ASI = 0x02 Capacity 16 KB Bank 1:Address = 0x0000000H to 0x00001fe0H (+32) Bank 2:Address = 0x8000000H to 0x80001fe0H (+32) Capacity 8 KB Bank 1:Address = 0x0000000H to 0x00000fe0H (+32) Bank 2:Address = 0x8000000H to 0x80000fe0H (+32) Capacity 4 KB Bank 1:Address = 0x0000000H to 0x000007e0H (+32) Bank 2:Address = 0x8000000H to 0x800007e0H (+32) Capacity 2 KB Bank 1:Address = 0x8000000H to 0x00003f0H (+16) Bank 2:Address = 0x8000000H to 0x800003f0H (+16) Capacity 1 KB Bank 2:Address = 0x8000000H to 0x800003f0H (+16)
bit \rightarrow 31	1 0
	Reserved
bit 0 :Entry Lock (Lock = 1, Unlock = 0, RS (2)Data Tag Lock Bit (DCLOCK)[Wite only]	ASI = 0x03 Capacity 16 KB Bank 1:Address = 0x00000000 to 0x00001fe0н (+32) Bank 2:Address = 0x80000000 to 0x80001fe0н (+32) Capacity 8 KB Bank 1:Address = 0x00000000 to 0x00000fe0н (+32) Bank 2:Address = 0x80000000 to 0x80000fe0h (+32) Capacity 4 KB Bank 1:Address = 0x00000000 to 0x000007e0h (+32) Bank 2:Address = 0x80000000 to 0x800007e0h (+32) Capacity 2 KB Bank 1:Address = 0x00000000 to 0x000003f0h (+16)
	Bank 2:Address = 0x8000000н to 0x800003f0н (+16) Capacity 1 KB
bit→ <u>31</u>	Capacity 1 KB
bit→ 31	Capacity 1 KB Bank 2:Address = 0x8000000н to 0x800003f0н (+16)

bit 0 :Entry Lock (Lock = 1, Unlock = 0, RST = 0)

(3)Instruction	Cache Tag (ICTAG)	Ba Capac Ba Capac Ba Capac Ba Ba Capac	ity 1 nk 2 nk 2 nk 2 nk 2 nk 2 nk 2 nk 2 nk 2	6 K :Ada :Ada :Ada :Ada :Ada :Ada :Ada :Ada	dres dres dres dres dres dres dres dres	s = 0x00000s = 0x80000s = 0x80000	000 000 000 000 000 000	н to н to н to н to н to н to н to н to	0x800 0x000 0x800 0x000 0x800 0x000 0x800	01fe0 00fe0 00fe0 007e0 007e0 003f0 003f0	н (+ н (+ н (+)н (+)н (+ н (+ н (+	32) 32) 32) -32) -32) 16) 16)
bit \rightarrow 31		13	12	11	10	9	6	5	4	2	1	0
	Address Tag											
bit 12 bit 11 bit 10 bit 9 to bit 6 bit 4 to bit 2 bit 5 bit 1 bit 0 *:BANK only, B X:Don't care	:Capacity 16 KB = <reserved>, Othe :Capacity 16 KB, 8 KB = <reserved> :Capacity 16 KB, 8 KB, 4 KB = <sub Capacity 2 KB, 1 KB = <address ta<br="">:Sub Block Valid (Valid = 1, Invalid = :Capacity 16 KB, 8 KB, 4 KB = <sub Capacity2 KB, 1 KB = <reserved> [:User/Supervisor (User = 0, Supervis :Capacity1 KB = <reserved>, Other= :Entry Lock (Lock = 1, Unlock = 0, RS ANK 2 is Reserved</reserved></reserved></sub </address></sub </reserved></reserved>	, Other Block V g> 0,RST = Block V Don't ca or = 1, F = LRU (F	= <a alid> = 0) alid> are fo ST</a 	\ddr >(Va >(Va >(Va or re = X	ress alid = alid = ad]	= 1, Invalid =						
(4)Instruction bit→ _31	Cache Invalidate Register (ICINVLD	ASI = Capac Ba Ba Other Ba	0x00 ity 1 nk 1 nk 2 nk 1	6 K :Ade :Ade :Ade	dres dres dres	s = 0x00008 s = 0x80008 s = 0x00001 s = 0x80001	000 000	н		2	1	0
		Reserve	d									
bit 31 to bit 2 bit 1 bit 0	:Reserved ["0"Write] :Cache LRU, Lock Bit Clear (Clear = :Valid Bit Clear (Clear = 1, Not Clear	-	lear	⁻ = 0))						<u> </u>	

bit 0 :Valid Bit Clear (Clear = 1, Not Clear = 0)

(5)Instruction (Cache Data RAM (ICDATA)	ASI = 0x0d
		Capacity 16 KB
		Bank 1:Address = 0x00000000 to 0x00001ffc+ (+4)
		Bank 2:Address = 0x8000000H to 0x80001ffcH (+4)
		Capacity 8 KB Bank 1:Address = 0x00000000н to 0x00000ffcн (+4)
		Bank 2:Address = $0x80000000 + t0 0x0000000000000000000000000$
		Capacity 4 KB
		Bank 1:Address = 0x00000000 to 0x000007fc+ (+4)
		Bank 2:Address = 0x80000000 to 0x800007fc+ (+4)
		Capacity 2 KB
		Bank 1:Address = 0x00000000H to 0x000003fcH (+4)
		Bank 2:Address = 0x8000000H to 0x800003fcH (+4)
		Сарасіty 1 КВ Bank 2:Address = 0x80000000н to 0x800003fсн
L it. 04		
bit→ 31		0
		Data
bit 31 to bit 0:Da	ata (RST = X)	
X:Don't care	, , , , , , , , , , , , , , , , , , ,	
(6)Data Cache	Tag (DCTAG)	
		Capacity 16 KB
		Bank 1:Address = 0x00000000 to 0x00001fe0+ (+32) Bank 2:Address = 0x80000000+ to 0x80001fe0+ (+32)
		Capacity 8 KB
		Bank 1:Address = 0x00000000 to 0x00000fe0H (+32)
		Bank 2:Address = 0x80000000 to 0x80000fe0+ (+32)
		Capacity 4 KB
		Bank 1:Address = 0x00000000 to 0x000007e0H (+32)
		Bank 2:Address = 0x80000000 to 0x800007e0+ (+32)
		Capacity 2 KB
		Bank 1:Address = 0x00000000 to 0x000003f0+(+16) Bank 2:Address = 0x80000000+ to 0x800003f0+ (+16)
		Capacity 1 KB
		Bank 2:Address = 0x80000000 to 0x800003f0+ (+16)
bit \rightarrow 31		13 12 11 10 9 6 5 4 2 1 0
	Address Tag	
	:Address Tag (RST = X)	
bit 12 bit 11	:Capacity 16 KB = <reserved>, Oth :Capacity 16 KB, 8 KB = <reserved< th=""><th></th></reserved<></reserved>	
bit 10		b Block Valid>(Valid = 1, Invalid = 0, RST = 0)
	Capacity 2 KB, 1 KB = <address t<="" th=""><th></th></address>	
bit 9 to bit 6	:Sub Block Valid (Valid = 1, Invalid =	= 0, RST = 0)
bit 4 to bit 2		b Block Valid>(Valid = 1, Invalid = 0, RST = 0)
	Capacity 2 KB, 1 KB = <reserved></reserved>	
bit 5	:User/Supervisor (User = 1, Supervi	,
bit 1 bit 0	:Capacity 1 KB = <reserved>, Othe</reserved>	

bit 0 :Entry Lock (Lock = 1, Unlock = 0, RST = 0)

*:BANK 1 only, BANK 2 is Reserved X:Don't care

(7)Data Cacho	e Invalidate Register (DCINVLD)[Wite only] ASI = 0x0e Capacity 16 KB Bank 1:Address = 0x00 Bank 2:Address = 0x80 Other Bank 1:Address = 0x00 Bank 2:Address = 0x80	0008000н 0001000н	
bit \rightarrow 31		2 1	0
	Reserved		
bit 31 to bit 2 bit 1 bit 0	:Reserved ["0"Write] :Cache LRU, Lock Bit Clear (Clear = 1, Not Clear = 0) :Valid Bit Clear (Clear = 1, Not Clear = 0)		
(8)Data Cach	Bank 2:Address = 0x80 Capacity 8 KB Bank 1:Address = 0x00 Bank 2:Address = 0x80 Capacity 4 KB Bank 1:Address = 0x00 Bank 2:Address = 0x80 Capacity 2 KB Bank 1:Address = 0x00 Bank 2:Address = 0x80 Capacity 1 KB	0000000н to 0x00001ffcн (+4 0000000н to 0x80001ffch (+4 0000000н to 0x80000ffch (+4 0000000н to 0x80000ffch (+4 0000000н to 0x800007fch (+4 0000000н to 0x800007fch (+4 0000000н to 0x800003fch (+4 0000000н to 0x800003fch (+4	4) 4) 4) 4) 4) 4)
bit \rightarrow 31			0
	Data		

bit 31 to bit 0 :Data (RST = X)

X:Don't care

16. Interrupt controller (IRC)

(1)Trigger Mode 0 Register (TRGM0) CS3# = L, Address<9:2> = 0x00 $bit \rightarrow$ 31 16 15 14 13 12 11 10 9 8 7 6 5 4 3 2 1 0 Reserved ch 15 ch 14 ch 13 ch 12 ch 11 ch 10 ch 9 ch 8 bit 31 to bit 16 :Reserved ["0"Write, Don't care for read] bit 15 to bit 0 :Trigger Mode (High Level = 00, Low Level = 01, High Edge = 10, Low Edge = 11, RST = 00) (2) Trigger Mode 1 Register (TRGM1) CS3# = L, Address<9:2> = 0x01 $bit \rightarrow$ 31 16 15 14 13 12 11 10 9 8 7 6 5 4 3 2 1 0 ch 7 ch 6 ch 5 ch 4 ch 3 Reserved ch 2 ch 1 00 bit 31 to bit 16 :Reserved ["0"Write, Don't care for read] :Trigger Mode (High Level = 00, Low Level = 01, High Edge = 10, Low Edge = 11, RST = 00) bit 15 to bit 2 bit 1 to bit 0 :Reserved ["0"Write, Read"0"] (3)Request Sense Register (REQSNS)[Read only] CS3# = L, Address<9:2> = 0x02 $bit \rightarrow$ 31 16 15 0 1 Reserved Request Sense 15 to Request Sense 1 0 bit 31 to bit 16 :Reserved [Don't care for read] :Request Sense 15 to Request Sense 1 (RST = 0) bit 15 to bit 1 :Reserved [Read"0"] bit 0 (4)Request Clear Register (REQCLR)[Wite only] CS3# = L, Address<9:2> = 0x03 $bit \rightarrow$ 31 16 15 1 0 0 Request Clear 15 to Request Clear 1 Reserved bit 31 to bit 16 :Reserved ["0"Write] :Request Clear 15 to Request Clear 1 (Clear = 1, Not Clear = 0) bit 15 to bit 1 bit 0 :Reserved ["0"Write]

(5)Interrupt Mask Register (IMASK)

$bit \rightarrow$	31 16	15 1	0
	Reserved	Mask 15 to Mask 1	IM

CS3# = L, Address<9:2> = 0x04

bit 31 to bit 16 :Reserved ["0"Write, Don't care for read]

bit 15 to bit 1 :Mask 15 to Mask 1 (Mask = 1, Not Mask = 0, RST = 1)

bit 0 :IRL Mask (Mask = 1, Not Mask = 0, RST = 0)

(6)IRL Latch/C	Clear Register (IRLAT)		C	S3#	= L	, Adc	Iress	s<9:2	> = 0x	05
bit→ 31	16	15				5	4	3		0
	Reserved		Rese	erved			CL		IRL	
bit 31 to bit 16 bit 15 to bit 5 bit 4 bit 3 to bit 0	:Reserved ["0"Write, Don't care for read] :Reserved ["0"Write, Read"0"] :IRL Clear [Wite only] (Clear = 1, Not Clear = 0) :IRL Latch [Read only] (RST = 0000)									
(7)IRC Mode F	Register (IMODE)		C	CS3#	= L	, Add	ress	<9:2>	> = 0x	06
bit \rightarrow 31	16	15							2 1	0
	Reserved			Res	erve	ed			IR	CMD
bit 31 to bit 16 bit 15 to bit 2 bit 1 to bit 0 17. DRAM co	:Reserved ["0"Write, Don't care for read] :Reserved ["0"Write, Read"0"] :IRC Mode [IRCMD] (Disable = 00, Enable = 01	, RST =	00)							
	Configuration Register (DBANKR)		C	CS3#	= L,	Add	ress	<9:2>	• = 0x(08
bit→ 31		11 10	98	7	6		4	3		0
ERR	Reserved	STA	DR H	E		COL		В	KSIZE	
bit 31 bit 30 to bit 11 bit 10 to bit 9 bit 8 bit 7 bit 6 to bit 4 bit 3 to bit 0 X:Don't care	:Access Error [ERR] (Error = 1, No Error = 0, RS :Reserved ["0"Write, Don't care for read] :DRAM Start Address [STADR] (RST = 01) :Hyper Page Enable [HE] (Page Mode DRAM = :DRAM Type[TP] (4CAS-1WE= 0, 4WE -1CAS :Column Address [COL] (RST = 011) :Bank Size [BKSIZE] (RST = 0011)	0, EDC	DRAN			T = 0))			
(2)DRAM Timi	ng Register (DTIMR)		C	S3#	= L,	Add	ress	<9:2>	• = 0 x()9
bit→ 31					5	4	3	2	1	0
	Reserved					Trps	Tras	SCBR	Tcas	Trp
bit 31 to bit 5 bit 4 bit 3 to bit 2 bit 1	:Reserved ["0"Write, Don't care for read] :RAS#Precharge time specification bits [T _{RPS}] at :RAS#Pulse width specification bit [T _{RASCBR}] at C (1 Cycle = 00, 2 Cycle = 01, 3 Cycle = 10, RST :CAS#Pulse width specification bit [T _{CAS}] (1 Cycl	BR Ref = 01)	resh				Cycl	e = 1	, RST	= 1)

- bit 1 :CAS#Pulse width specification bit [TcAs] (1 Cycle = 0, 2 Cycle = 1, RST = 1)
- bit 0 :RAS#Precharge width specification bit $[T_{RP}]$ (1 Cycle = 0, 2 Cycle = 1, RST = 0)

18. DSU (Debugging support unit)(MB86832/834)

(1)Instruction Address Descriptor Register (INSTADR) ASI

DR) ASI = 0x01, Address = 0x0000ff00+ to 0x0000ff04+

bit \rightarrow 31	2	1 0
	Instruction Address Compare Data	Reserved
bit 31 to bit 2 bit 1 to bit 0	:Instruction Address Compare Data (RST = 0x00000000н) :Reserved ["0"Write, Don't care for read]	
(2)Data Addre	ess Descriptor Register (DATAADR) $ASI = 0x01$, Address = $0x0000ff08$ to $0x$: 0000ff0с н
bit \rightarrow 31		0
	Data Address Compare Data	
bit 31 to bit 0	:Data Address Compare Data (RST = 0x0000000н)	
(3)Data Value	Descriptor Register (DVDR) ASI = 0x01, Address = 0x	: 0000ff10 н
bit \rightarrow 31		0
	Data Value	
bit 31 to bit 0	:Data Value (RST = 0x0000000н)	
(4)Data Value	Descriptor Register/Mask Register (DVDMSK) ASI = 0x01, Address = 0x	: 0000ff14 н
bit \rightarrow 31		0
	Data/Mask Value	
bit 31 to bit 0	:Data/Mask Value (RST = 0x0000000н)	
(5)Debug Cor	ntrol Register (DSUCR) ASI = 0x01, Address = 0x	: 0000ff18 н
bit \rightarrow 31	24 23 16 15 14 13 9 8 7 6 5 4 3 2	2 1 0
	ASI Value2 ASI Value1 Reserved ASI Value2	
bit 31 to bit 24 bit 23 to bit 16 bit 15 bit 14 bit 13 to bit 9 bit 8 bit 7 bit 6 bit 5 bit 4 bit 3 to bit 2	 :ASI Value2 (RST = 0x00) :ASI Value1 (RST = 0x00) :Instruction User/Supervrisor2 (Supervrisor = 1, User = 0, RST = 0) :Instruction User/Supervrisor1 (Supervrisor = 1, User = 0, RST = 0) :Reserved :Enable Data Address2 Break (Enable = 1, Disable = 0, RST = 0) :Enable Data Address1 Break (Enable = 1, Disable = 0, RST = 0) :Enable Instruction Address2 Break (Enable = 1, Disable = 0, RST = 0) :Enable Instruction Address1 Break (Enable = 1, Disable = 0, RST = 0) :Enable Instruction Address1 Break (Enable = 1, Disable = 0, RST = 0) :Enable Instruction Address1 Break (Enable = 1, Disable = 0, RST = 0) :Enable Instruction Address1 Break (Enable = 1, Disable = 0, RST = 0) :Enable Instruction Address1 Break (Enable = 1, Disable = 0, RST = 0) :Enable Instruction Address1 Break (Enable = 1, Disable = 0, RST = 0) :Enable Instruction Address1 Break (Enable = 1, Disable = 0, RST = 0) 	

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MB86830 Series

bit 3	bit 2	Туре
0	0	Break only on Loads
0	1	Break only on Stores
1	0	Break on Load or Store
1	1	Break Always

bit 1 :Data Value Condition (Outside = 1, Inside = 0, RST = 0)

bit 0 :Data Value Mask (Mask = 1, Range = 0, RST = 0)

(6)Debug Status Register (DSR)

ASI = 0x01, Address = $0x0000ff1C_H$

$\text{bit} \rightarrow$	31		6	5	4	3	2	1	0
		Reserved							
bit 31 to l bit 5 bit 4 bit 3 bit 2 bit 1 bit 0	bit 6	:Reserved ["0"Write, Don't care for read] :Data Address 2 Match (Match = 1, Not Match = 0, RST = 0) :Data Address 1 Match (Match = 1, Not Match = 0, RST = 0) :Instruction Address 2 Match (Match = 1, Not Match = 0, RST = 0) :Instruction Address 1 Match (Match = 1, Not Match = 0, RST = 0) :EMUENBL [Read only] :EMUBRK [Read only]							

19. Clock gear (Not supported in MB86831-66,80)

Internal Clock Control/Status Register (ICCS)

CS3# = L, Address<9:2> = 0x0b

$bit \rightarrow$	31 7	6 4	3	2	0
	Reserved	CLKST	CE	CLKSE	

bit 31 to bit 7 :Reserved ["0"Write, Don't care for read]

bit 6 to bit 4 :Internal Clock Status [CLKST]

bit 3 :Internal Clock Change Enable [CE] (Enable = 1, Disable = 0, RST = 0)

bit 2 to bit 0 :Internal Clock Select [CLKSEL]

CLKST	Internal Clock
100	× 1
101	× 2
110	× 3
111	× 4
011	× 5
010	
001	Reserved
000	

Register explanation

Internal Clock Control/Status Register (ICCS)

bit \rightarrow 31	7	6 4	3	2 0
	Reserved	CLKST	CE	CLKSEL
bit 31 to bit 7 bit 6 to bit 4	:Reserved ["0"Write, Don't care for read] :CLKST (Internal Clock Status)(An initial value is a set point of extern CLKSEL1, and CLKSEL0.) Can know the multiplication rate that CPU works by the bit which sh			
	CLKST Internal Clock			
	100 × 1			
	101 × 2			
	110 × 3			
	111 × 4			
	011 × 5			
	010			
	001 Reserved			
	000			
bit 3 bit 2 to bit 0	 :CE (Internal Clock Change Enable)(Initial value "0") Internal Clock change inable bit.Internal Clock is changed according to this value at sleep mode (low power consumption mode). 1: Internal Clock is changed by the CLKSEL bit. 0: No change Internal Clock. It is necessary to set "1" in this bit to change Internal Clock before sl sumption mode) is set. :CLKSEL (Internal Clock Select) Internal Clock specification bit. 			
20. General-	ourpose 16-bit Timer (MB86836)			
(1) Prescaler	D (PRS0) CS3# = L	., Address<	9:2>	= 0x0c
bit \rightarrow 31	16 15 14 13 11 10 8	37		0

$DII \rightarrow$	31	16	15	14	13 11	10 8	1		0
		Reserved	EX	Test	Reserved	Select		Prescale Value	
bit 31 to b bit 15 bit 14 bit 13 to b		:Reserved ["0"Write, Don't care f :External Clock ["0"Write] Support to only internal clock mo :Test ["0"Write] :Reserved ["0"Write, Don't care f	ode	-					
bit 10 to b bit 7 to bit		:Select (RST = 000) :Prescale Value (RST = 01)							

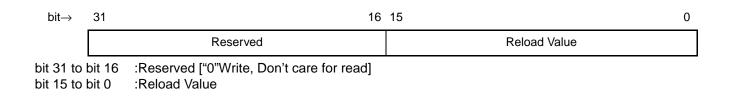
(2) Timer Control Register (TCR)

CS3# = L, Address<9:2> = 0x0d

bit \rightarrow 31	16	15	14	13	12	11	10	9	8	7	6	5	3	2	0
	Reserved														
bit 31 to bit 16 bit 15 bit 14 bit 13 bit 12 bit 12 bit 11 bit 10 to bit 9 bit 8 to bit 7 bit 6 bit 5 to bit 3 bit 2 to bit 0	:Reserved ["0"Write, Don't care for read] :Value Of OUT Signal :Value Of IN Signal :Reserved ["0"Write, Don't care for read] :Test ["0"Write] :Count Enable (Enable = 1, Disable = 0, F :Clock Select (Internal Clock = 0, Prescal :OUT Signal Control (Keep = 0, Set = 1, F :Invert (true = 0, Invert = 1, RST = 0) :Mode Select :Event Select	ler (Cloc	k =						or 3	3, R	ST =	0)		

(3) Reload Value Register (RVR)

CS3# = L, Address<9:2> = 0x0e



(4) Count Value Register (CVR) [Read Only]

CS3# = L, Address<9:2> = 0x0f

$\text{bit} \rightarrow$	31	16	15	0
		Reserved	Count Value	
		:Reserved ["0"Write, Don't care for read]		

bit 15 to bit 0 :Count Value

For details on each register, refer to the manual for the MB86942.

21. Notes on Register Setting

(1)Cache/BIU Control Register

- To set Cache Enable or Cache Disable, be sure to insert at least three NOP instructions after the Enable or Disable instruction.
- The Non-Cacheable bit (bit 9, bit 8) and Cacheability Enable bit (bit 7) cannot be read.

(2)Bus Control Register

• Enable burst transfer after setting Cache Enable. To set Cache Disable, disable burst transfer in advance.

(3)System Support Control Register

- Set Cache Enable before setting DRAM Burst Enable. To set Cache Disable, disable the DRAM Burst Enable bit.
- Before setting DRAM Burst Enable, be sure to set Burst Enable using the Bus Control Register.
- The SAMEPAGE# pin may become "L" at the first CS4 access after setting Same Page Enable.
- The Same Page circuit holds previous data even after the bus master is changed.
- Set the Same Page Mask Register before setting Same Page Enable to "1".
- Before changing the Same Page Enable (bit 5) setting, set Cache Disable.
- Set all of the Address Range Specifier Registers and Address Mask Registers before setting CS Enable to "1". (Set all of the Address Range Specifier Registers and Address Mask Registers even if any CS is not to be used.)
- Before changing the CS Enable (bit 4) setting, set Cache Disable.
- When setting the Programmable Wait-state, be sure to set the Wait State Specifier Register.

(4)Wait State Specifier Register

- Do not set the Wait Enable bit and the Single Cycle Non Burst Mode bit to "1" at the same time.
- If the Single Cycle Non Burst Mode bit is set to "1" in the burst mode, the ready signal is generated in one cycle regardless of the setting of the Single Cycle Burst Mode bit.
- When setting the CS3 Wait State Specifier Register, be sure to set the Override bit to"1". (The Wait State bit can also be set to "1".)

When the half-word load instruction is executed with CS3 in 16-bit Bus Mode, the CPU accesses twice but the ready signal from the peripheral resource is generated only once. Therefore the CPU hangs at the second access. To generate the second ready signal, set the Wait Enable bit to "1" (the CPU discards the data received at the second access).

(5)Bus Width/Cacheable Register

- In the DRAM Controller Enable state with CS4# = "L", CS5 is handled as a Non-Cacheable signal.
- In the DRAM Controller Enable state, the CS5 bus width follows the CS4 bus width setting. When the CS4 Bus Width Control bit has been set to (10) ₂, for example, the CS5 bus width is forced to be set to (10) ₂.
- The CS3 Bus Width can be set only to the 16-bit or 32-bit bus width. When the 16-bit bus width is set, use Half-Word Load (address "0") or Half-Word Store (address "0") to access the interrupt controller (IRC) and DRAM controller registers.

(6)DRAM Refresh Timer Register

- Be sure to set the Test Mode bit to "0". Otherwise, TOVF# may not become "L".
- Since the timer performs counting based on the external clock, it is not affected by the multiplier circuit.

(7)Sleep Mode Register

- To set the sleep mode (low power consumption mode), disable the caches.
- The instruction to set the sleep mode (low power consumption mode) must be followed by at least three NOP instructions.

(8) Trigger Mode Register

• Set the Interrupt Mask Register to (ffff)₁₆ before changing the Trigger mode.

• The Request Sense Register may contain "1" when the Trigger Mode is changed. Therefore, issue "Request Clear" before canceling interrupt masks.

The interrupt controller (IRC) and DRAM controller registers cannot be accessed until CS3# becomes"L".

(9)Cache Invalidate Register

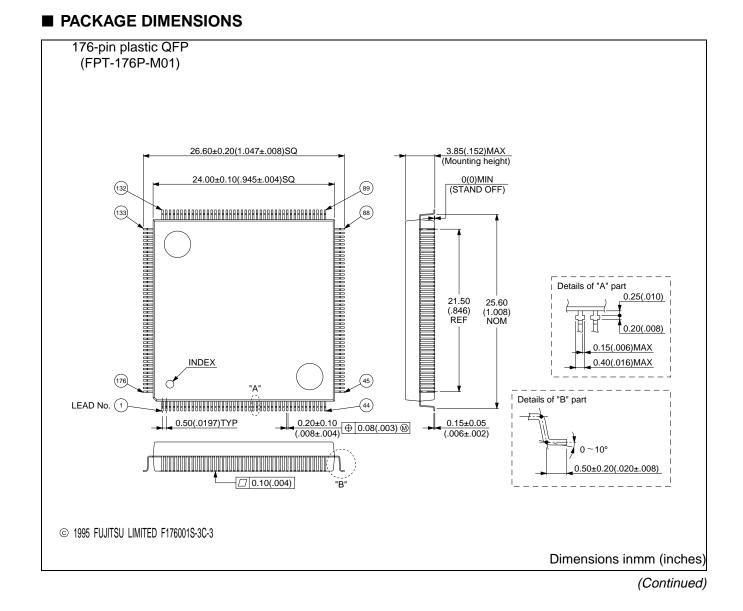
When the caches are off, write to the Cache Invalidate Register.

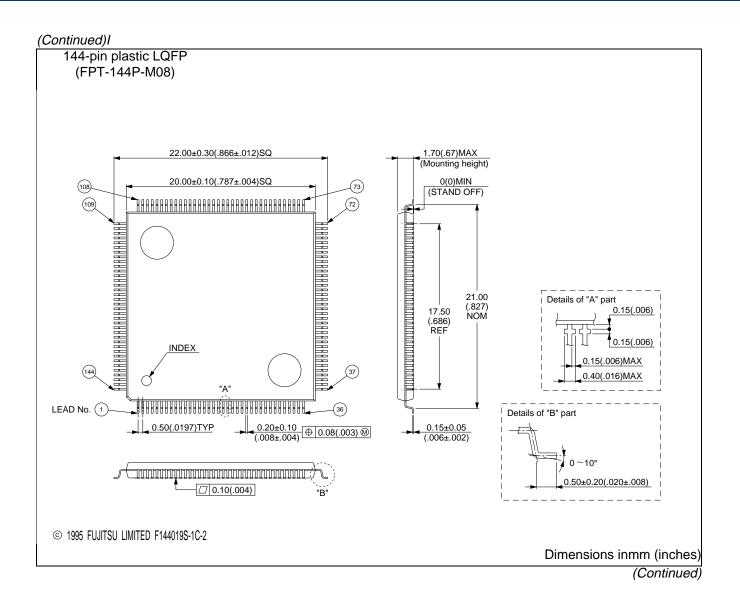
(10)Internal Clock Control/Status Register

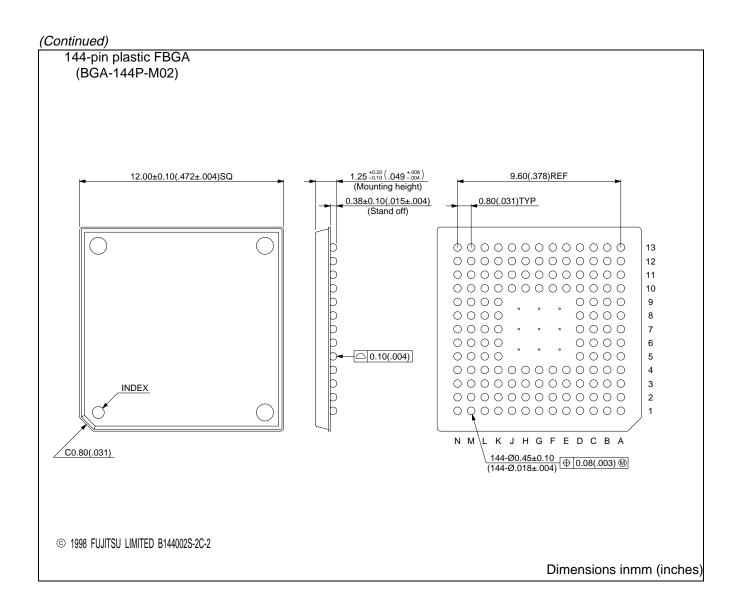
To change clock multiplication by setting the CE bit in the internal clock control/status register to "1", input the "L" pulse to the WKUP# pin at least 4000 CLKIN after entering the sleep mode.

■ ORDERINGINFORMATION

Part number	Package	Remarks
MB86831PFV	Plastic QFP 176-pin (FPT-176P-M01)	
MB86831-80PFV	Plastic QFP 176-pin (FPT-176P-M01)	
MB86832-66PFV	Plastic QFP 176-pin (FPT-176P-M01)	
MB86832- 80PFV	Plastic QFP 176-pin (FPT-176P-M01)	
MB86832-100PFV	Plastic QFP 176-pin (FPT-176P-M01)	
MB86833PMT2	Plastic LQFP 144-pin (FPT-144P-M08)	
MB86834PFV	Plastic QFP 176-pin (FPT-176P-M01)	
MB86834-120PFV	Plastic QFP 176-pin (FPT-176P-M01)	
MB86835PMT2	Plastic LQFP 144-pin (FPT-144P-M08)	
MB86836PMT2	Plastic LQFP 144-pin (FPT-144P-M08)	
MB86836-108PMT2	Plastic LQFP 144-pin (FPT-144P-M08)	Under development
MB86836PBT	Plastic FBGA 144-pin (BGA-144P-M02)	
MB86836-108PBT	Plastic FBGA 144-pin (BGA-144P-M02)	Under development







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